

可視赤外線観測装置技術ワークショップ

2月23日 14:30 -15:00



TOHOKU
UNIVERSITY

光MEMS

:Deformable mirror

東北大学大学院工学研究科
ナノメカニクス専攻
羽根 一博

1. 光MEMSの紹介

- ・マイクロミラー
- ・可変格子
- ・集積型センサ
- ・Si導波路干渉計

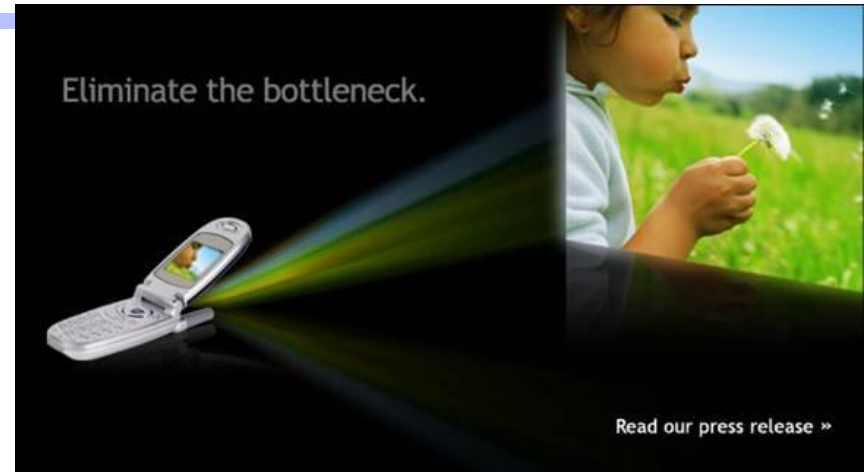
2. 焦点可変デフォーマブルミラーの製作

- ・曲げモーメント駆動による焦点可変ミラー
- ・焦点可変ミラーを備えた光スキャナー
- ・波面補償デフォーマブルミラーの製作

Applications of laser scanning to display



Automobile application

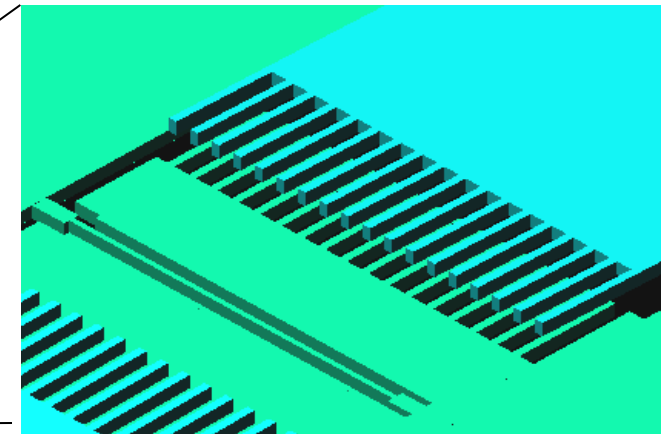
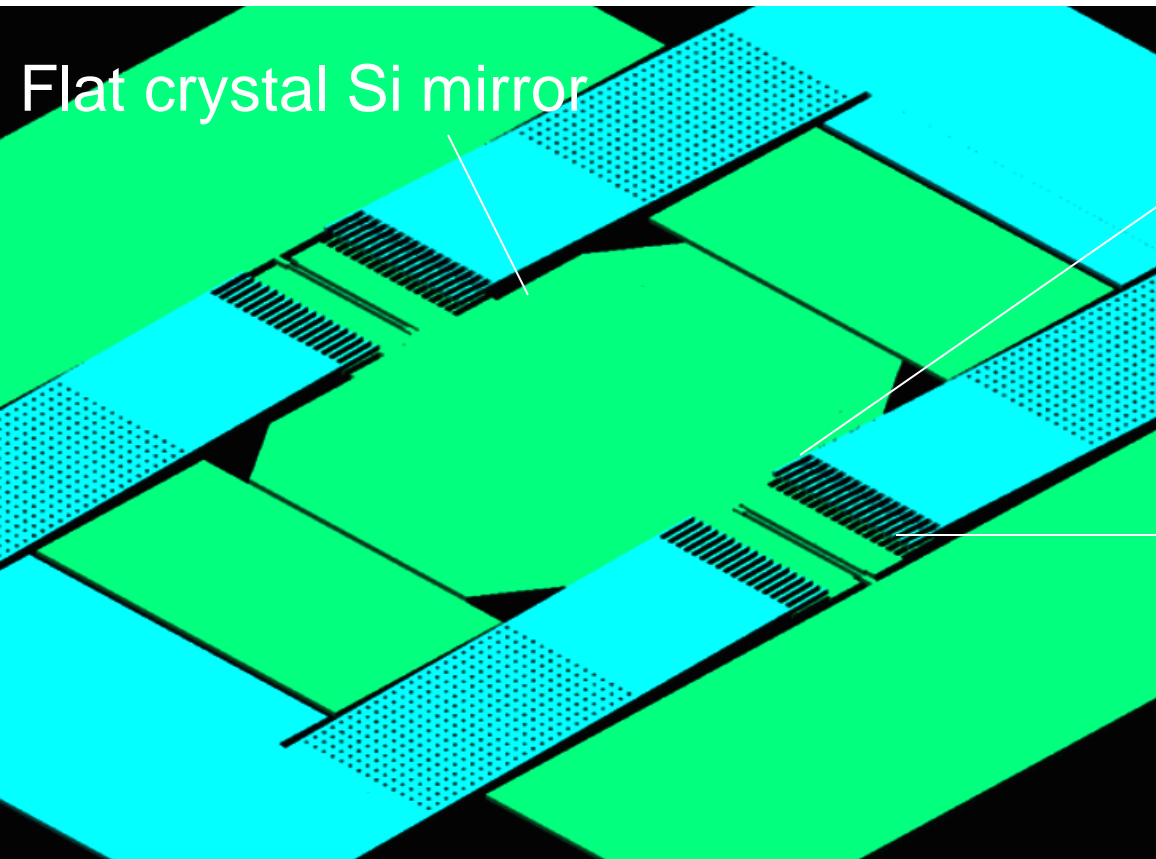


Bi-axial MEMS scanner



Mobile phone application

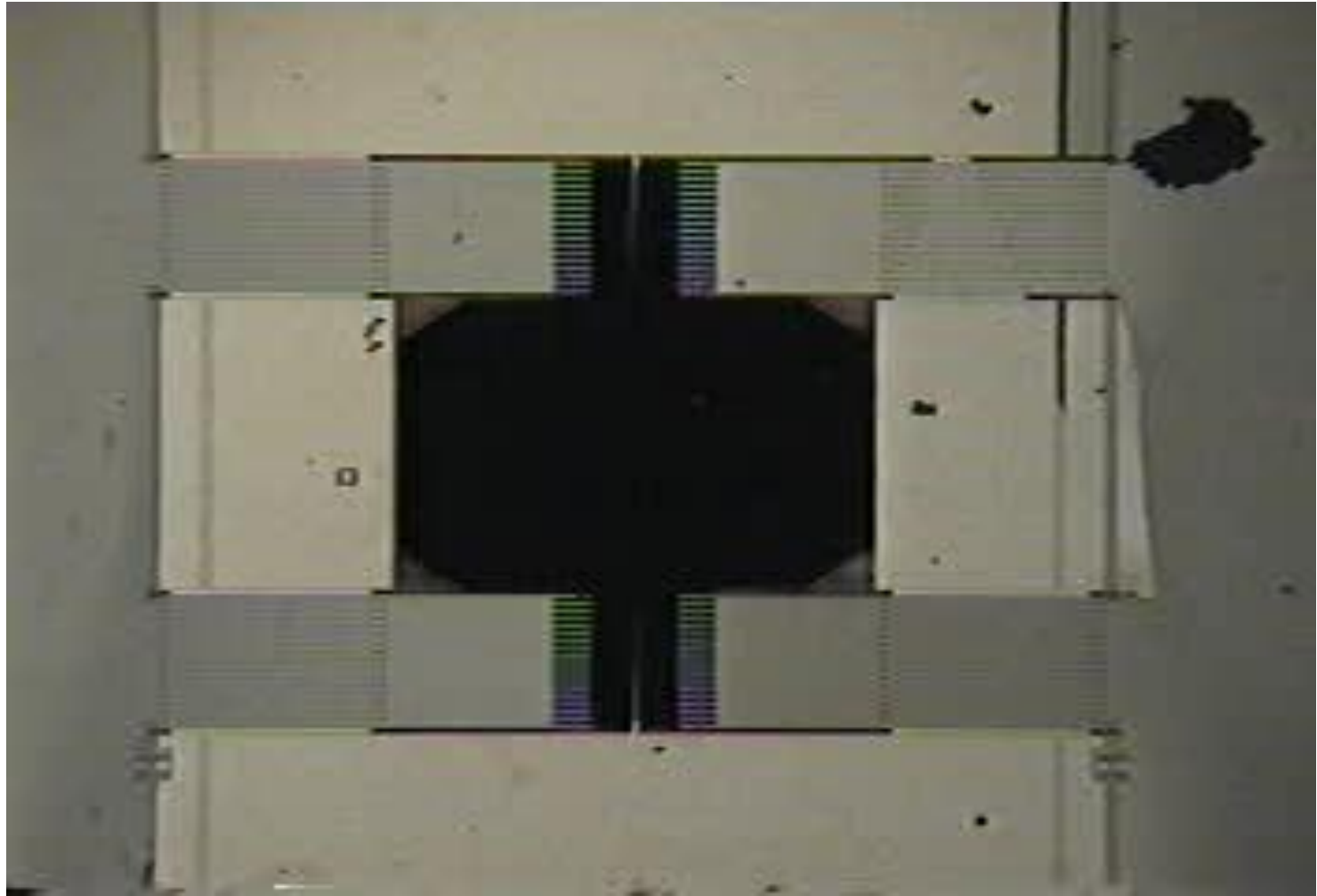
Crystal Si micro mirror fabricated from SOI wafer



Vertical comb drive actuator

While view of the micro mirror

Motion of Micro mirror

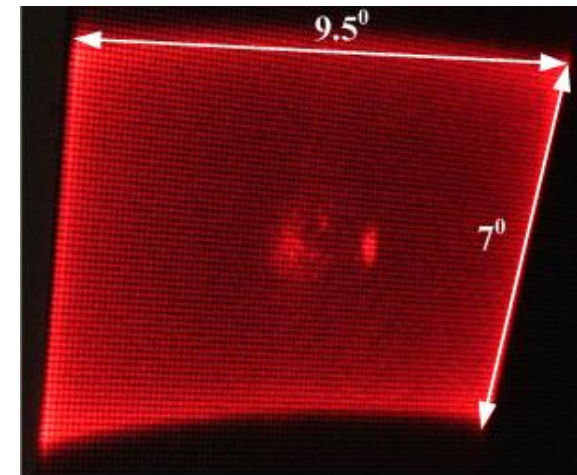


500 μ m

2軸静電くしスキャナ



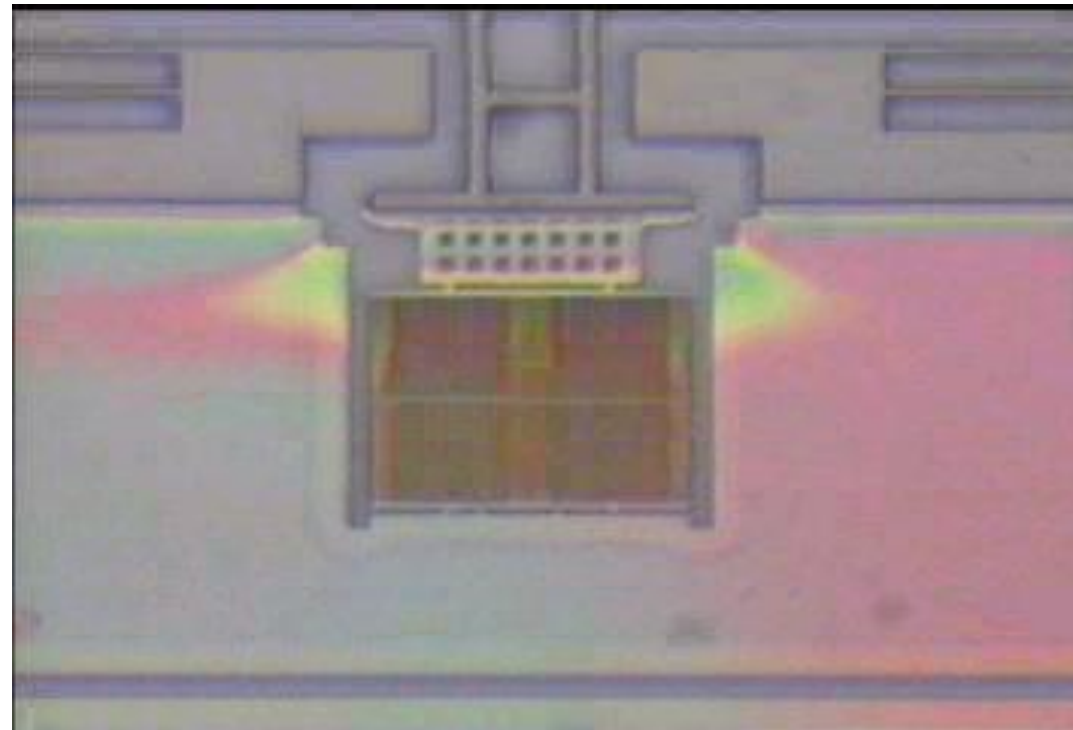
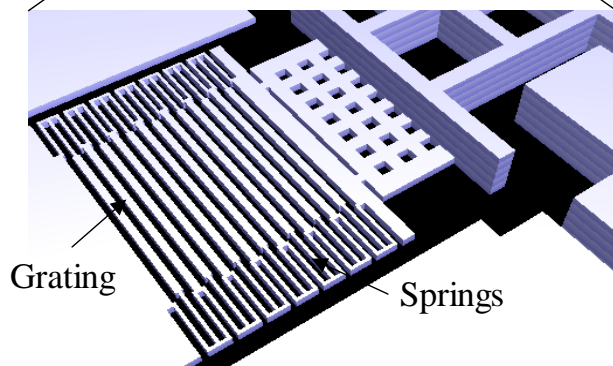
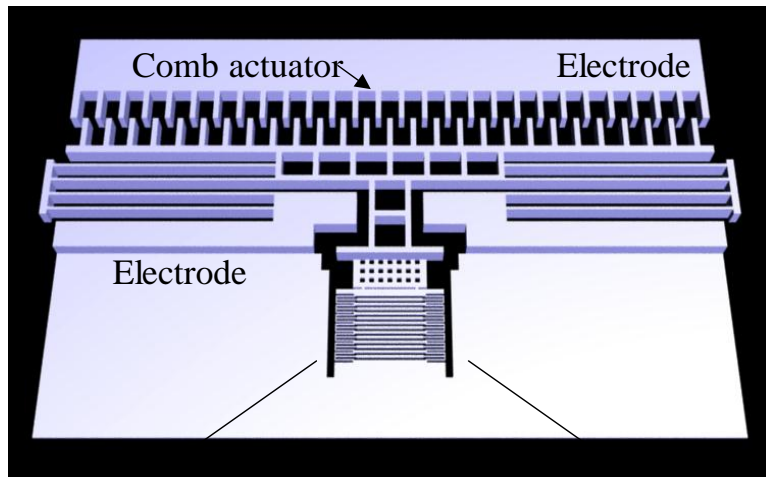
2軸静電くしスキャナ



スキャンイメージ

ミラー共振周波数: 40kHz
フレーム共振周波数: 162Hz
ミラー電圧: 12V(11.5度)
フレーム電圧: 10V(14度)
圧力: 1Pa 真空

Tunable gratings



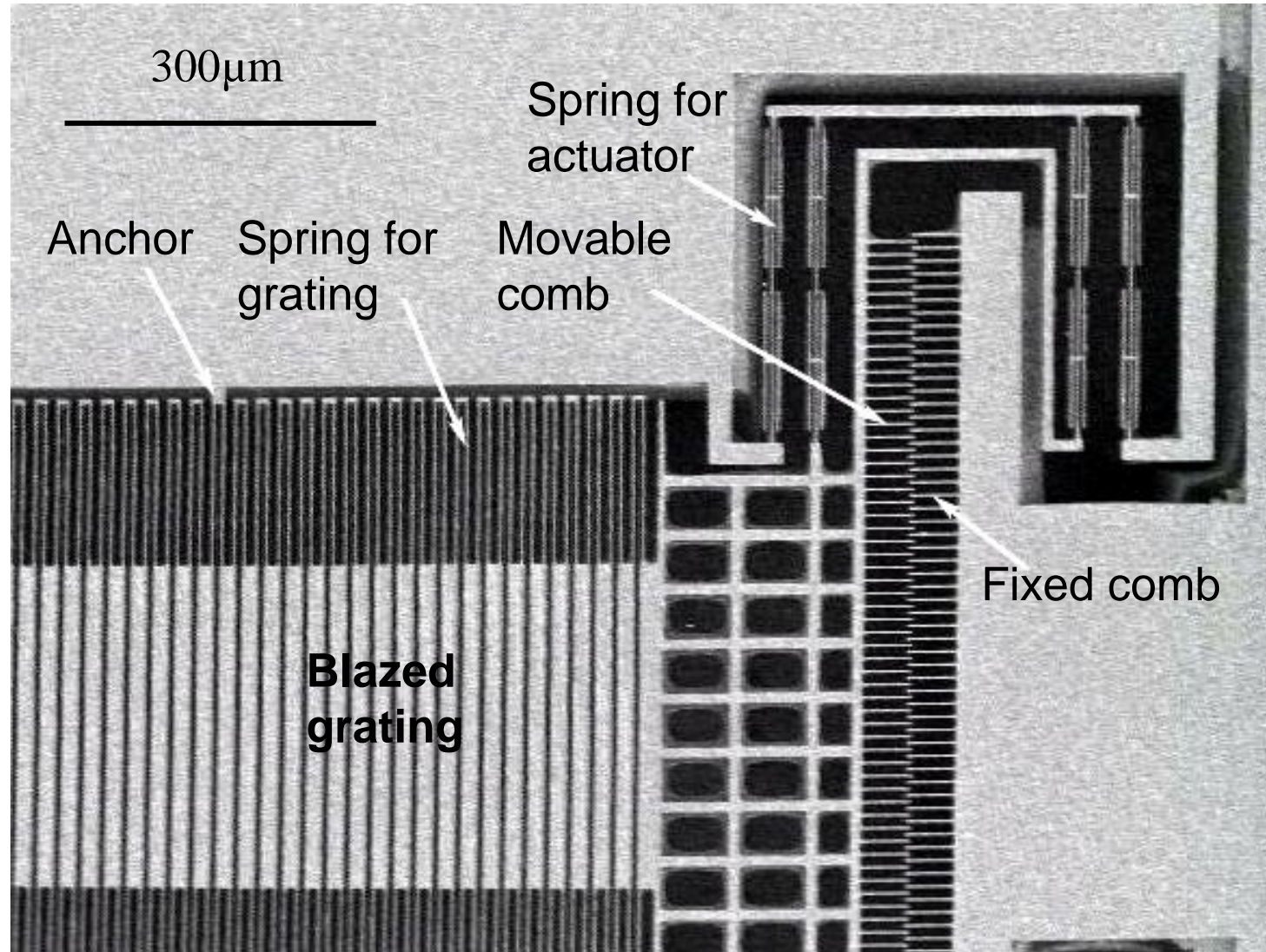
Design

- *Self-suspended thin grating (300nm)
- *Grating period : 600nm

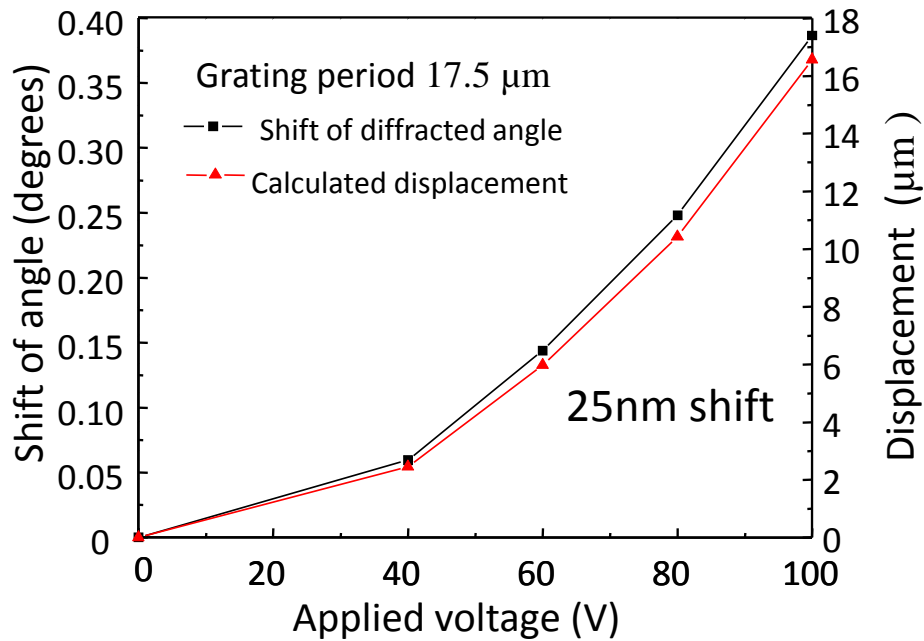
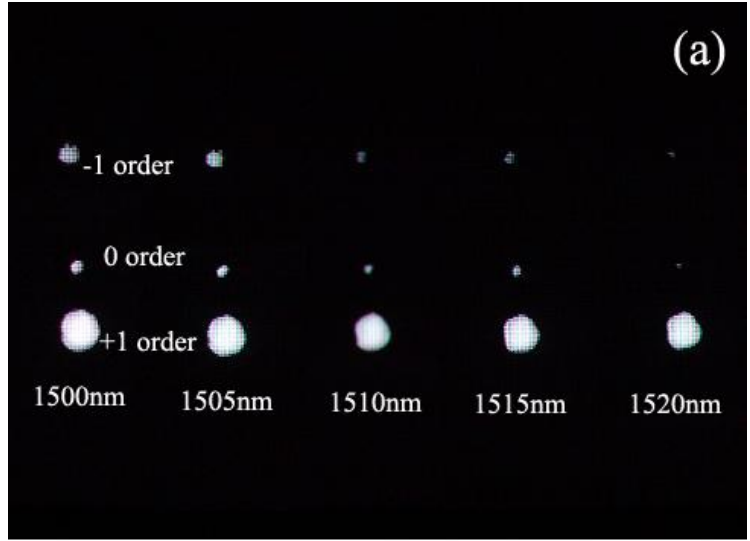
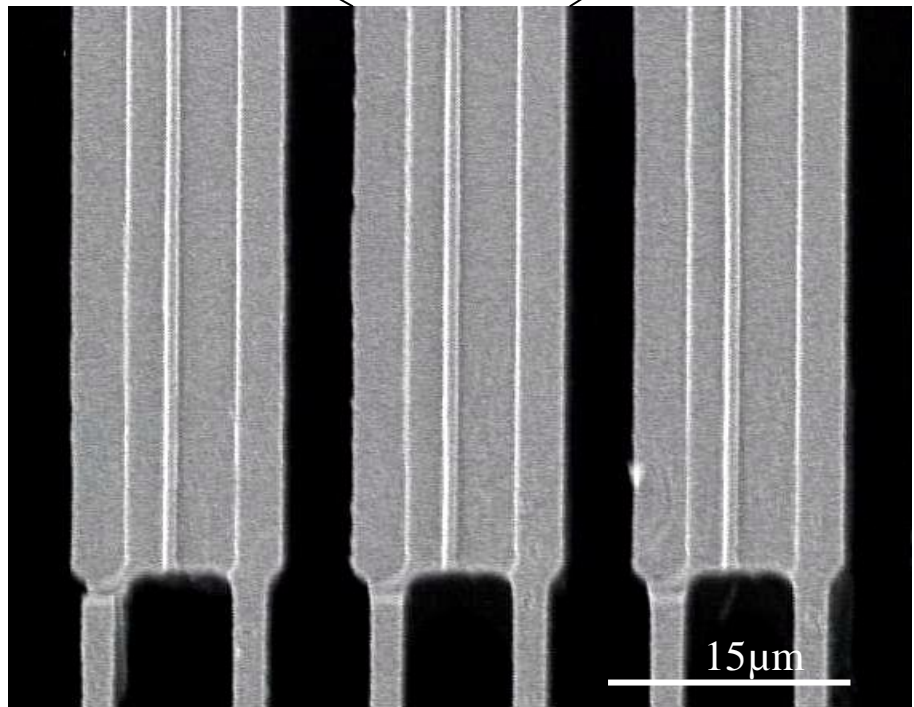
Fabrication

- *Self-suspended thin grating is connected a thick (5 μ m) actuator

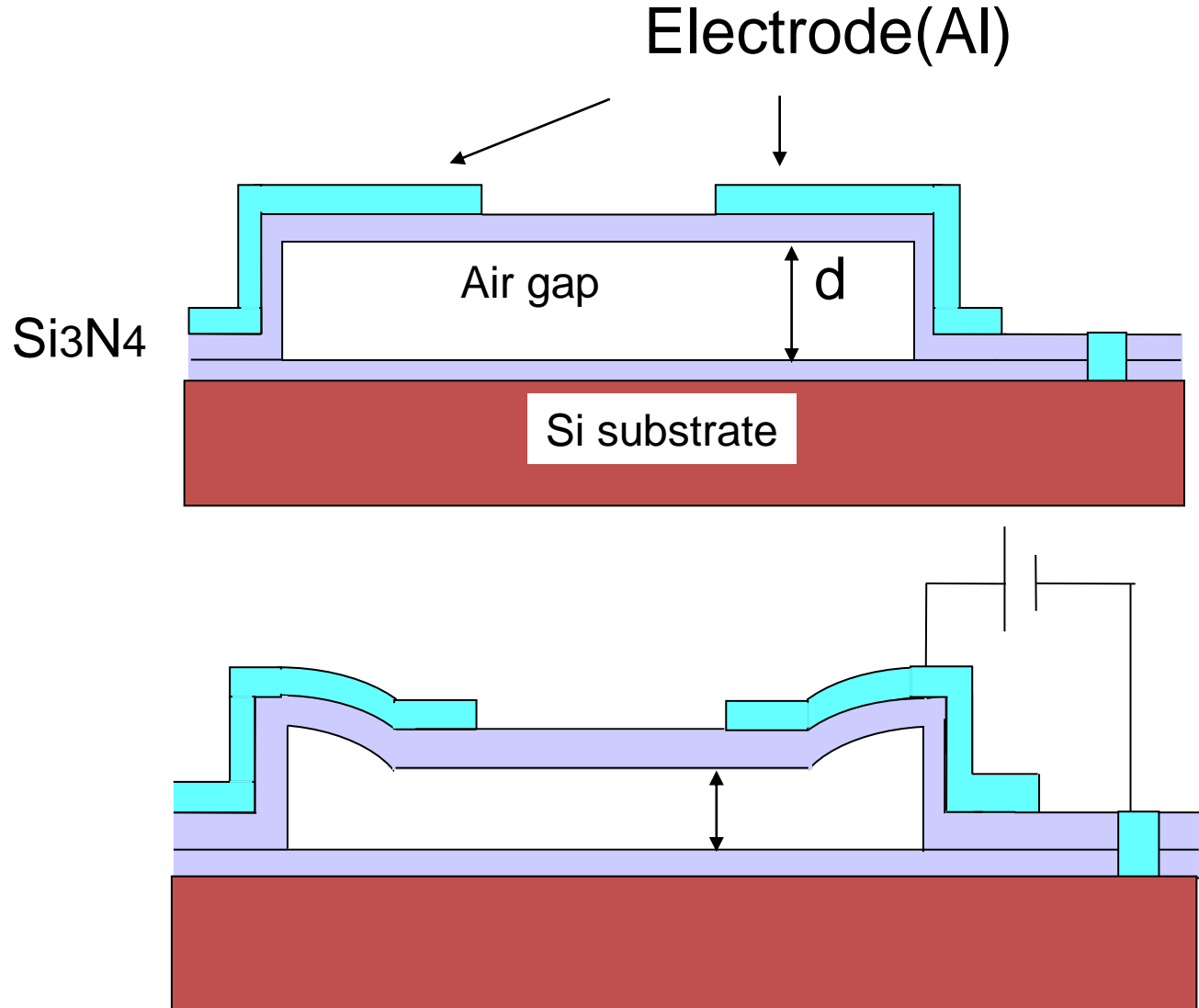
ブレードのある周期可変回折格子(1.5 μm 帯)



製作結果(ブレース格子部)と測定結果

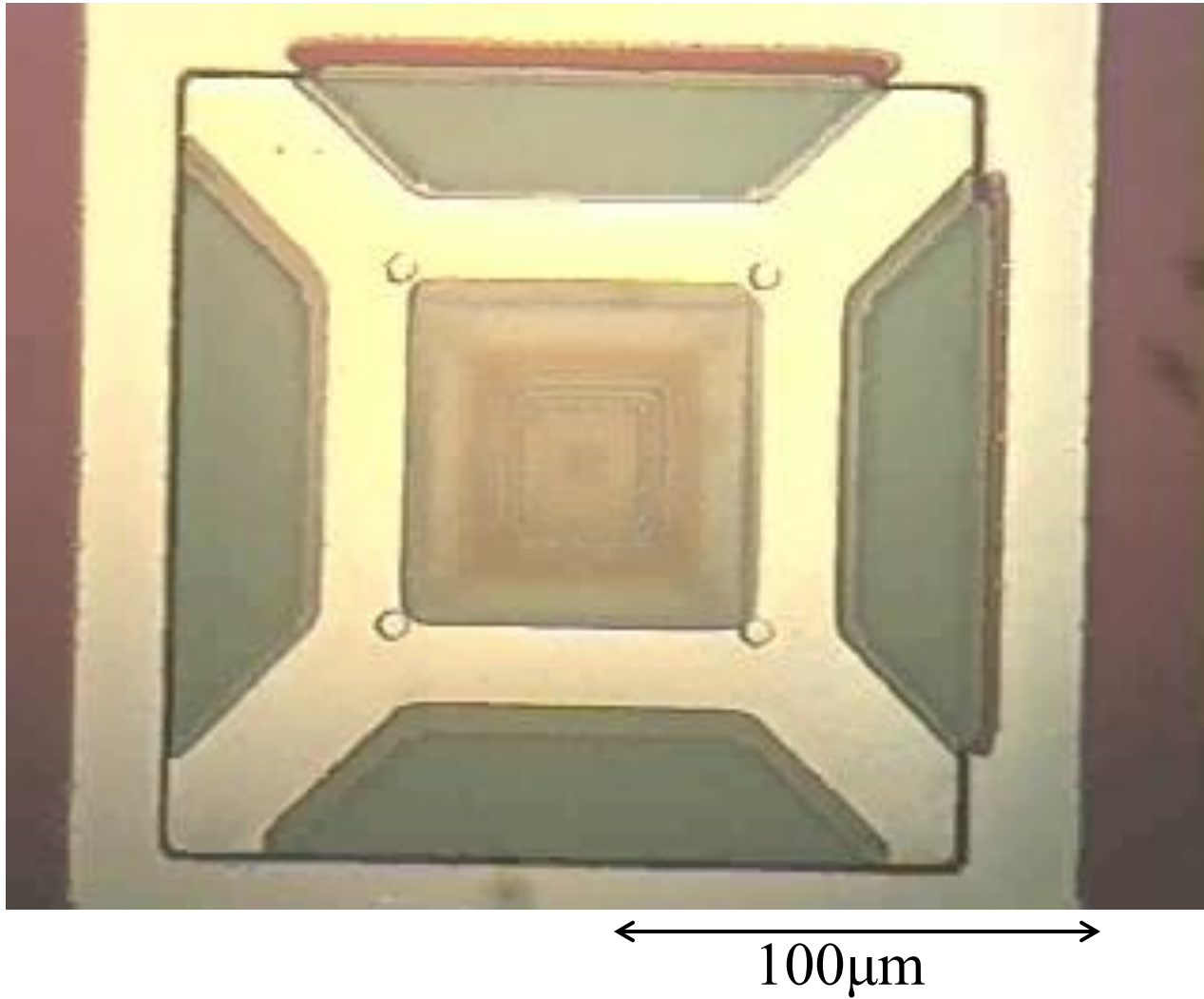


Principle of tunable Fabry-Perot filter



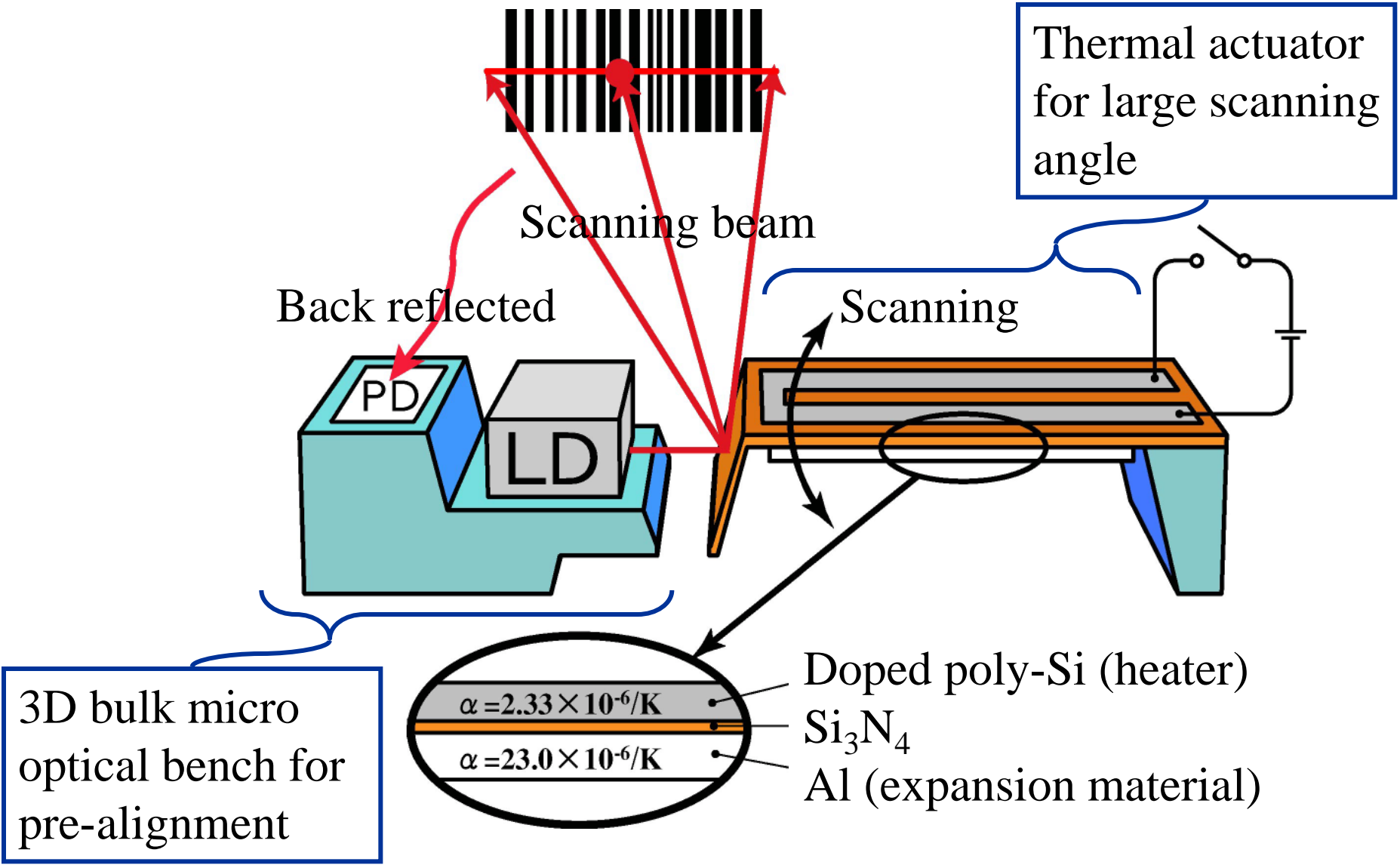
Reflection is controlled by changing gap

Movement of suspended membrane



White light illumination, $d_1=170\mu\text{m}$ $d_2=70\mu\text{m}$

3D integrated optical scanner



Thermal actuator for large scanning angle

Scanning beam

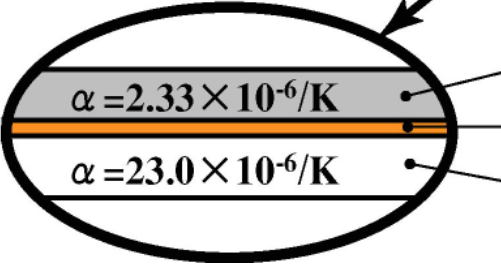
Back reflected

Scanning

PD

LD

3D bulk micro optical bench for pre-alignment



Doped poly-Si (heater)
 Si_3N_4
Al (expansion material)

Actuator motion

Twin type



Micro-mirror

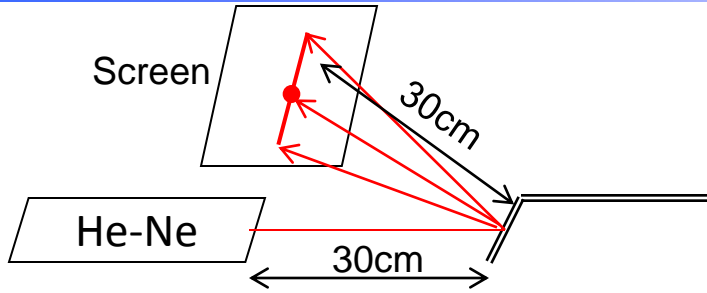
Single type



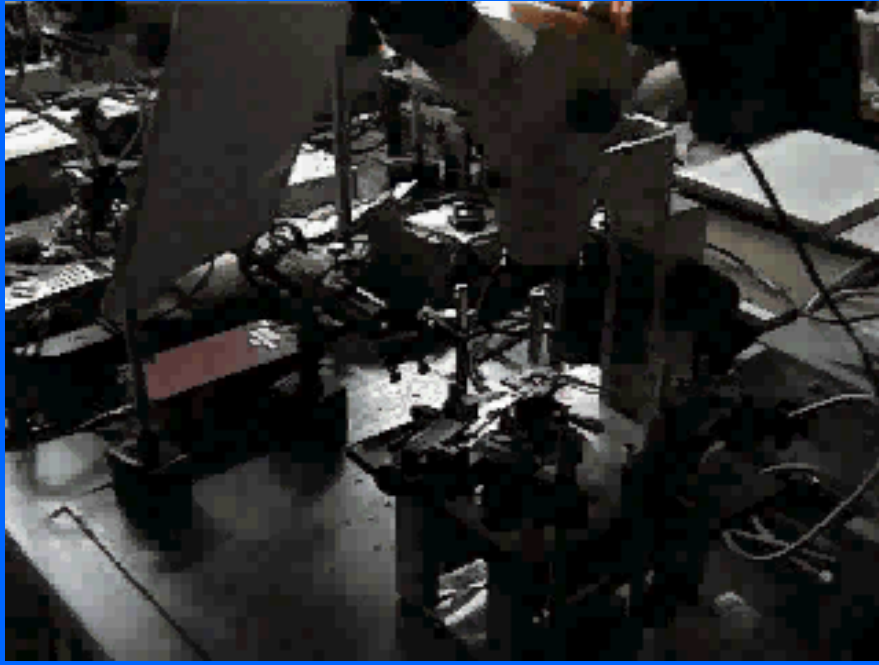
terrace for LD

Mirror angle over 15 deg. is obtained.
Driving voltage is 20 V.
Current is 6mA.

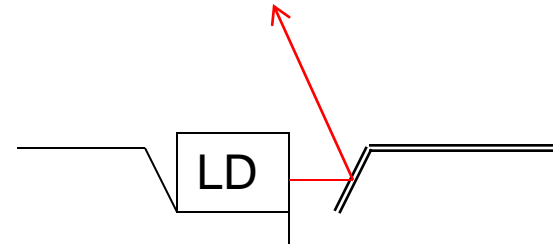
Beam scanning



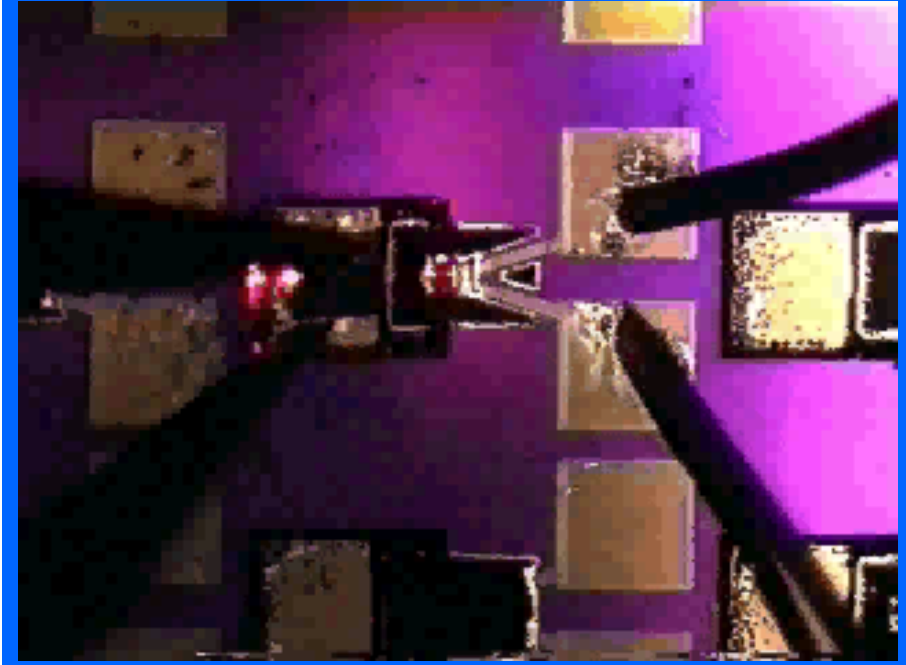
Scanning with He-Ne laser beam



Flat micro-mirror generates small spot.

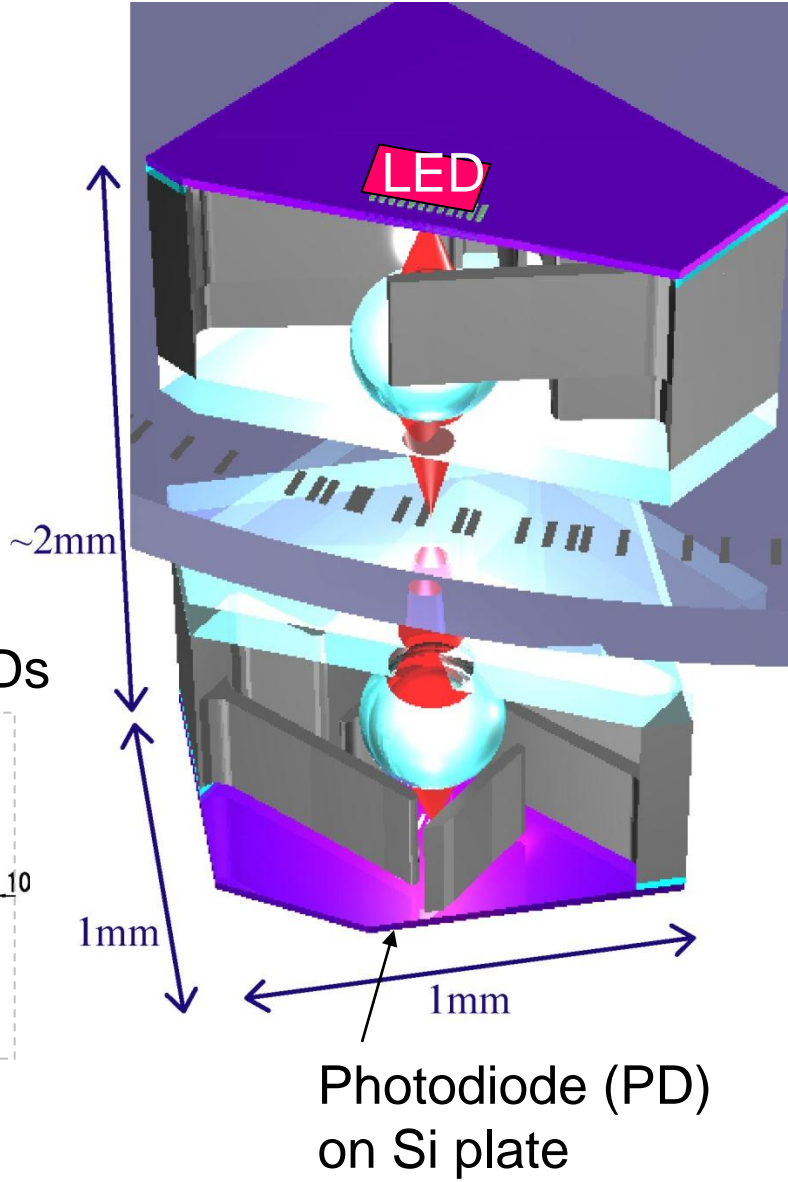
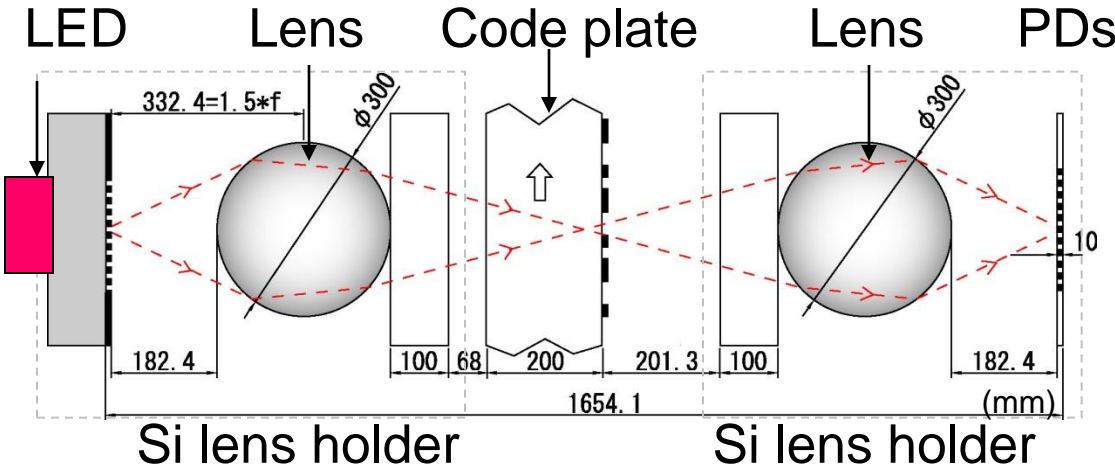
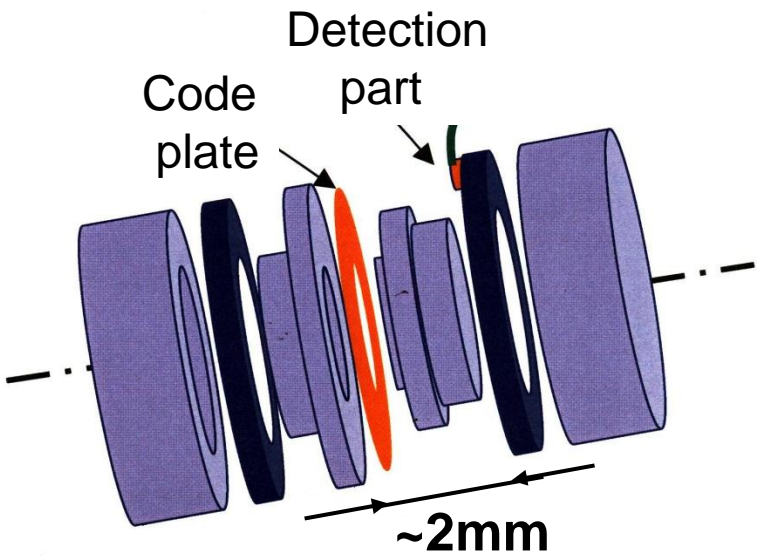


Scanner integrated with LD



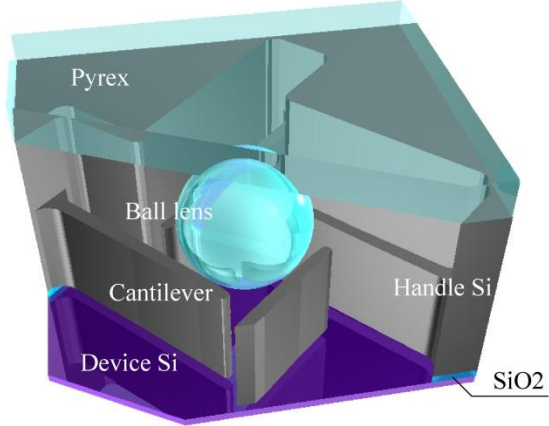
Only putting LD, optical axis is aligned.

Optical configuration of the encoder エンコーダの光学系

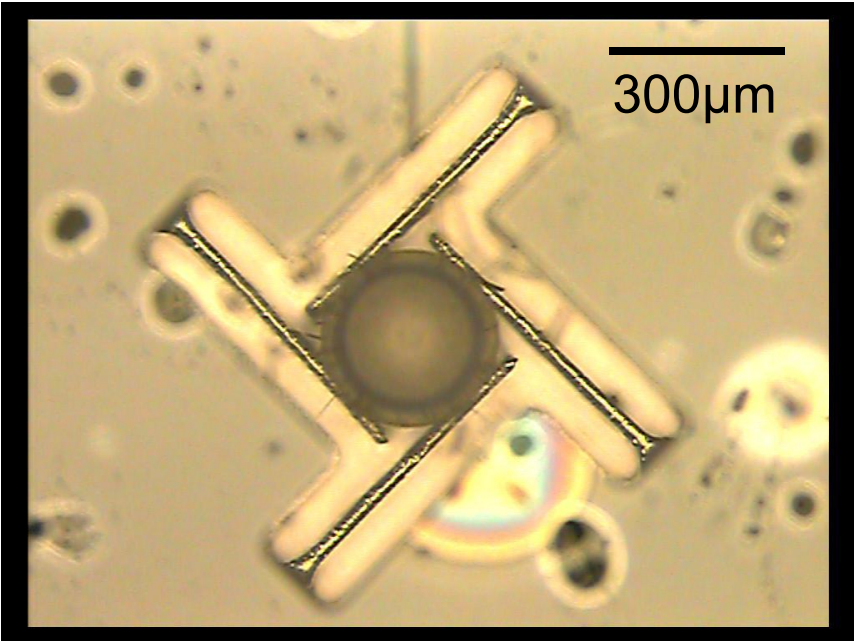


光検出部の製作結果

Silicon lens holder

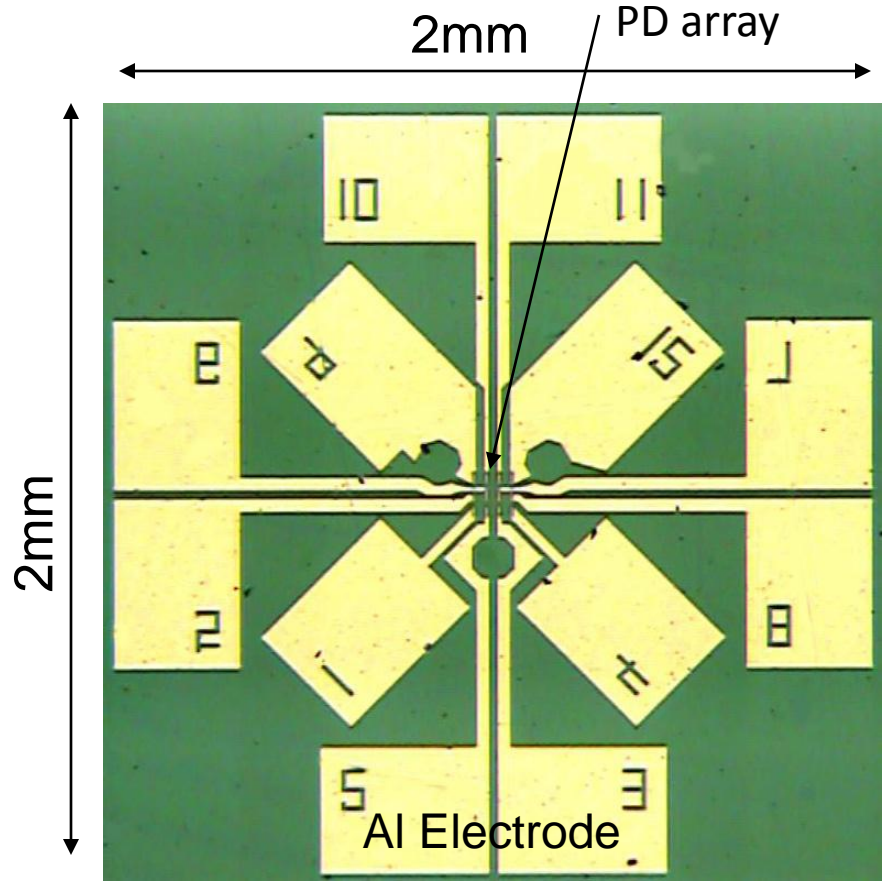
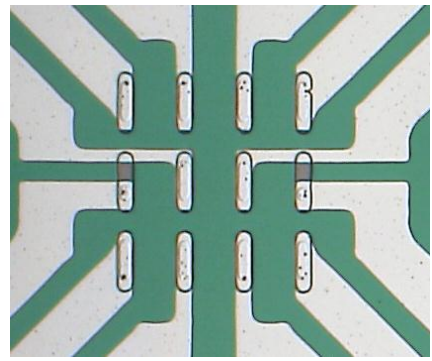


With lens



Alignment errors $< \pm 10\mu\text{m}$

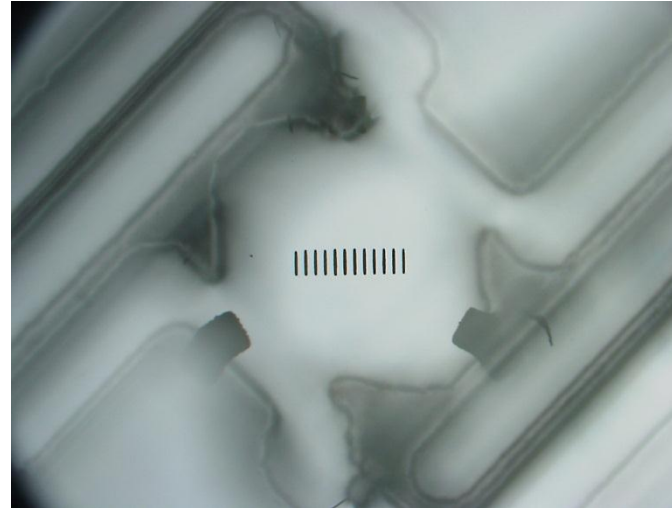
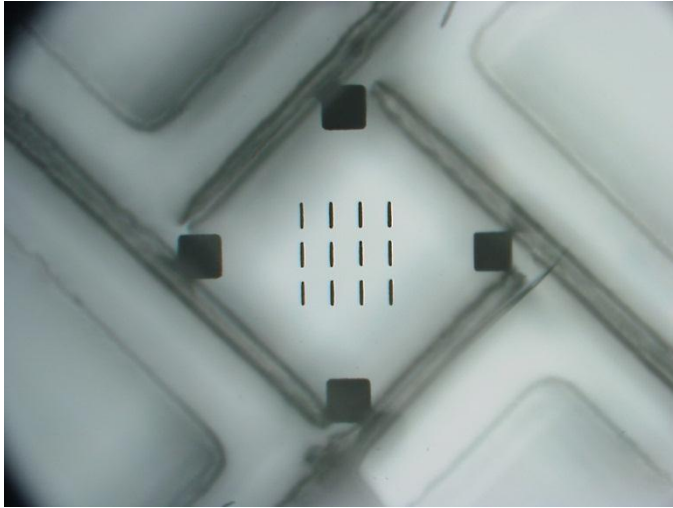
Photodiode array behind lens holder



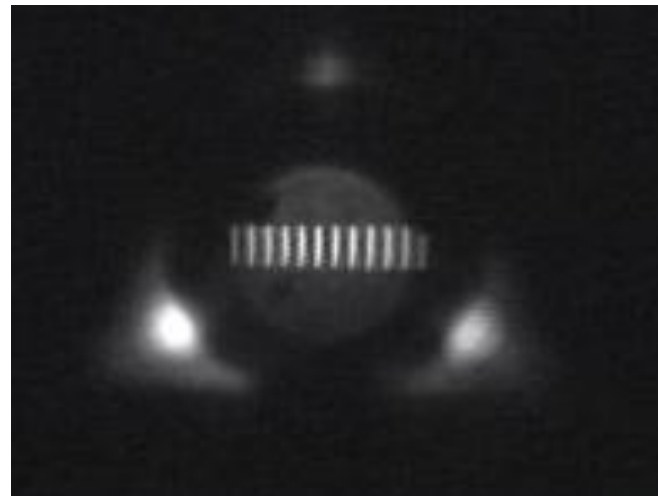
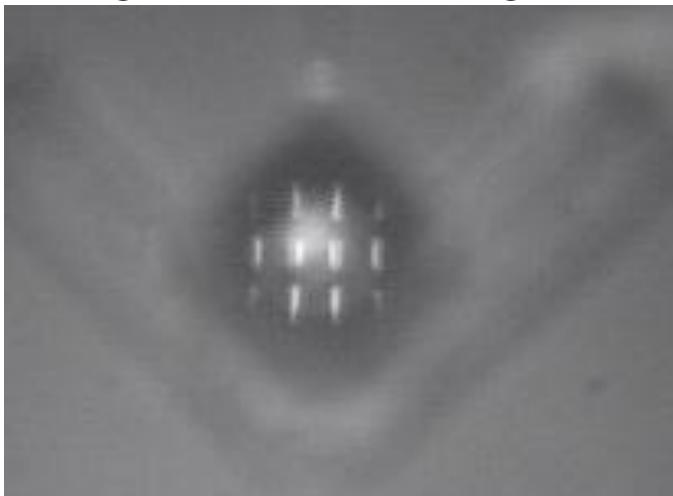
PD array: 2x2x0.6mm, 3 x4 diodes

光源部の製作結果

Light source slits on Si top layer of SOI wafer



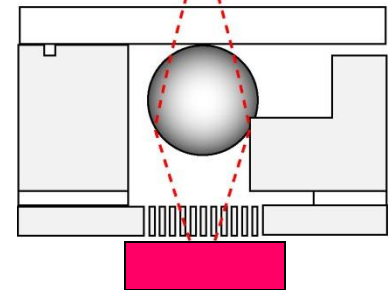
Images of slits through ball lens



Slit size

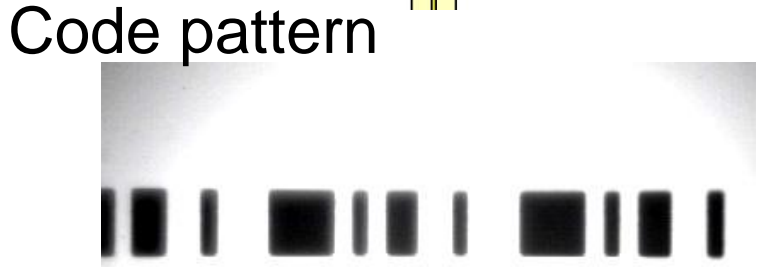
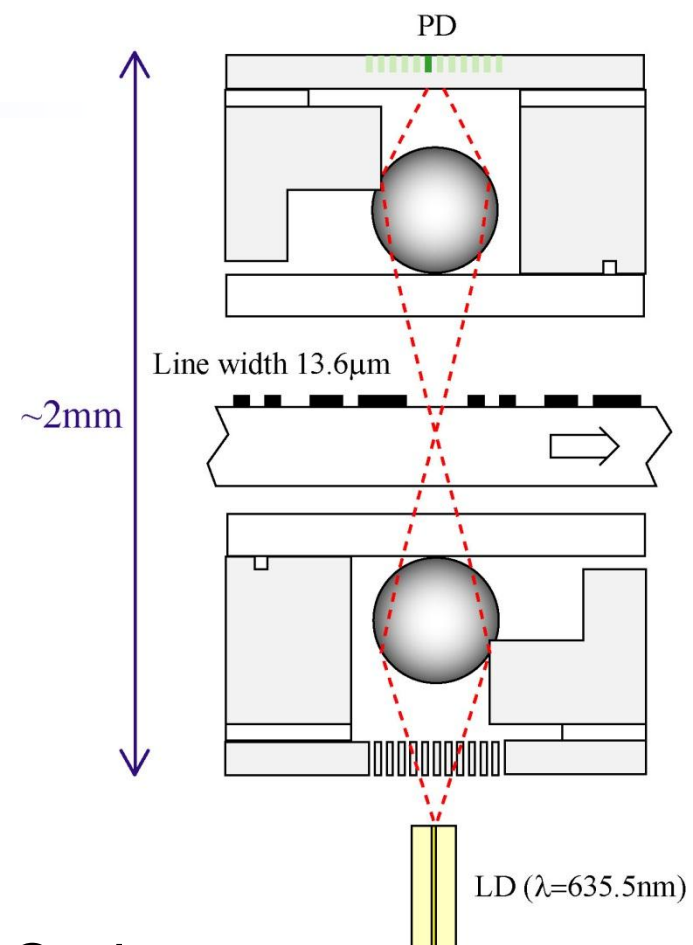
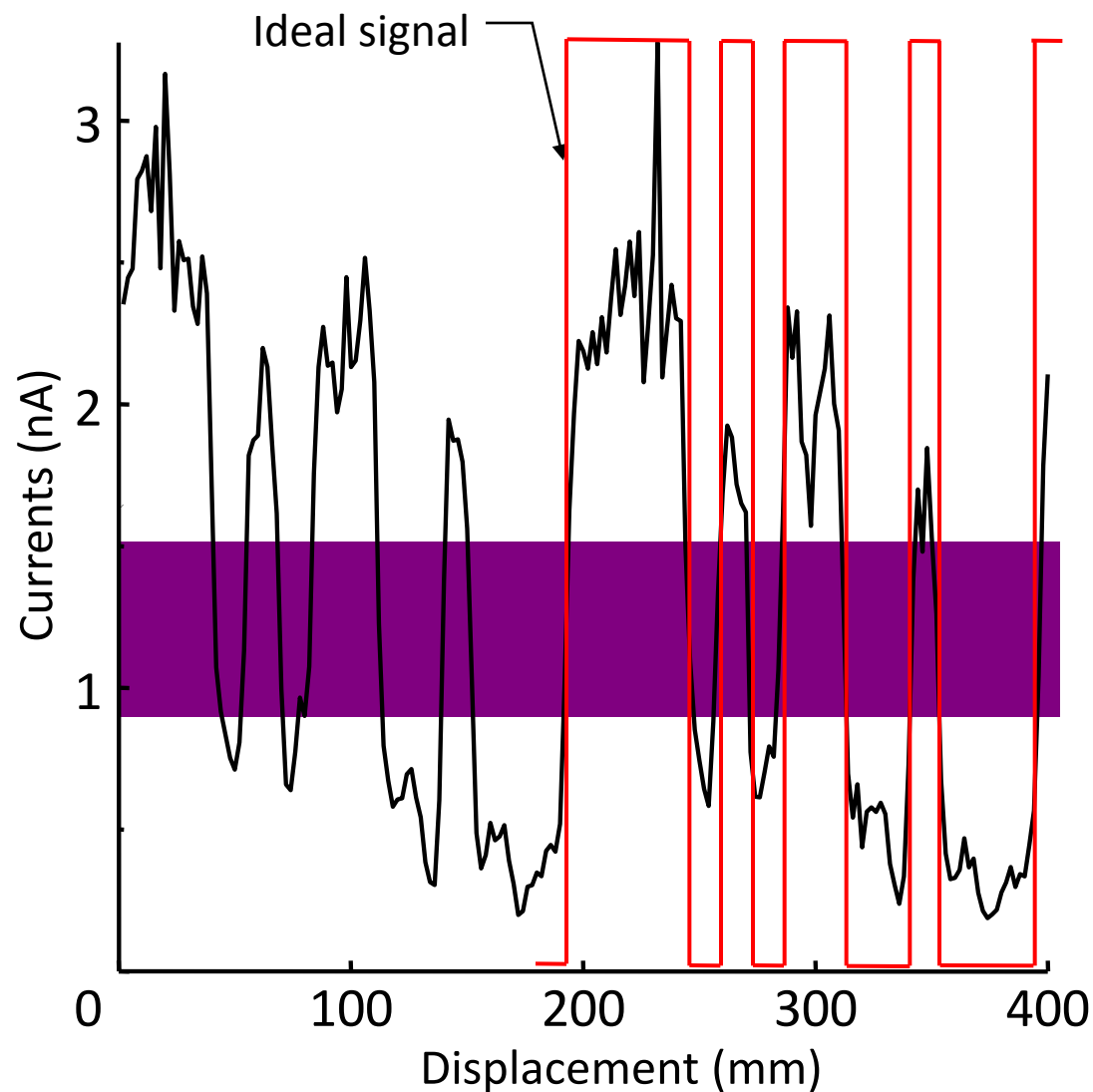
5 μ m wide
30 μ m long

focal position



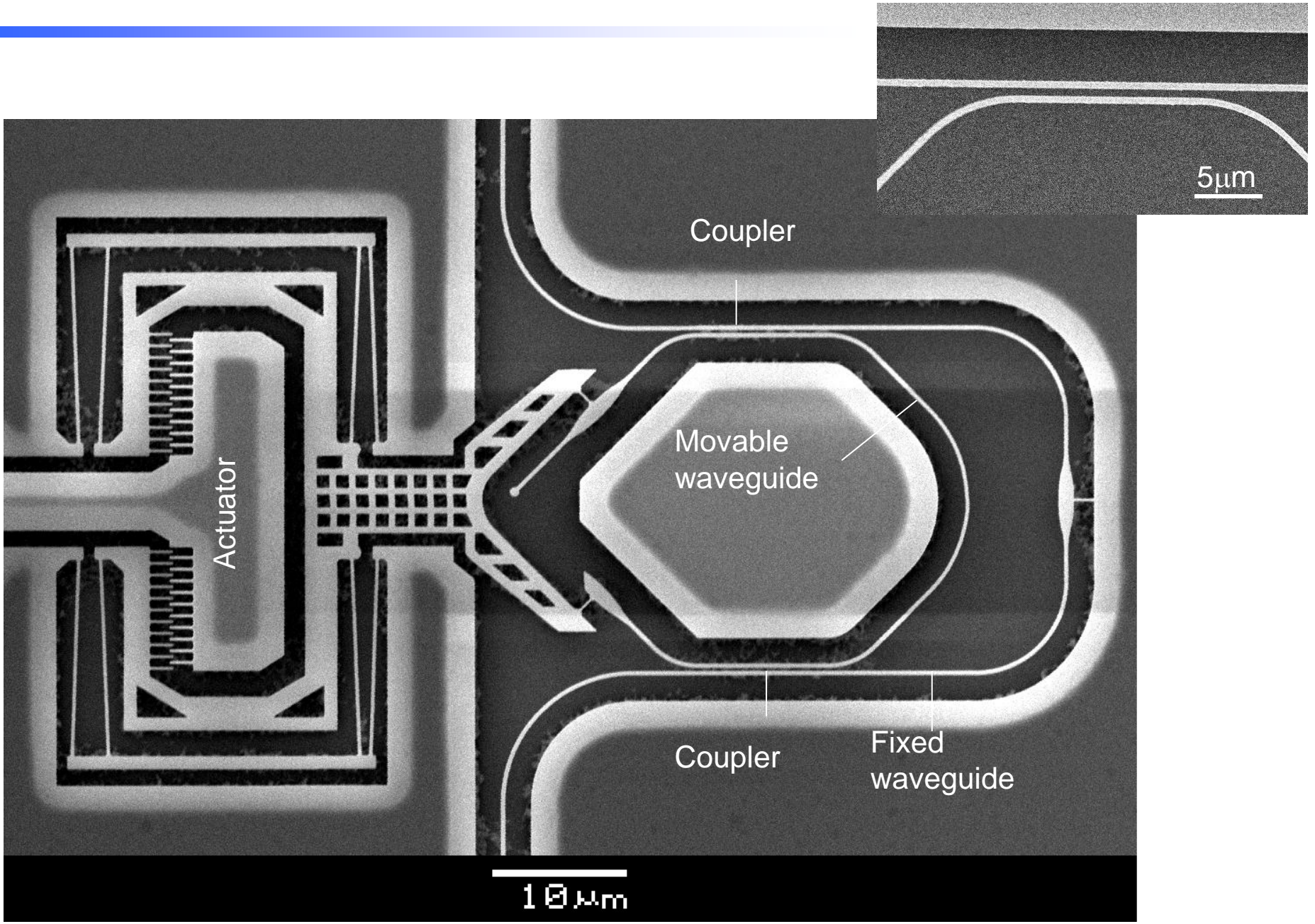
LED

測定したエンコーダ信号



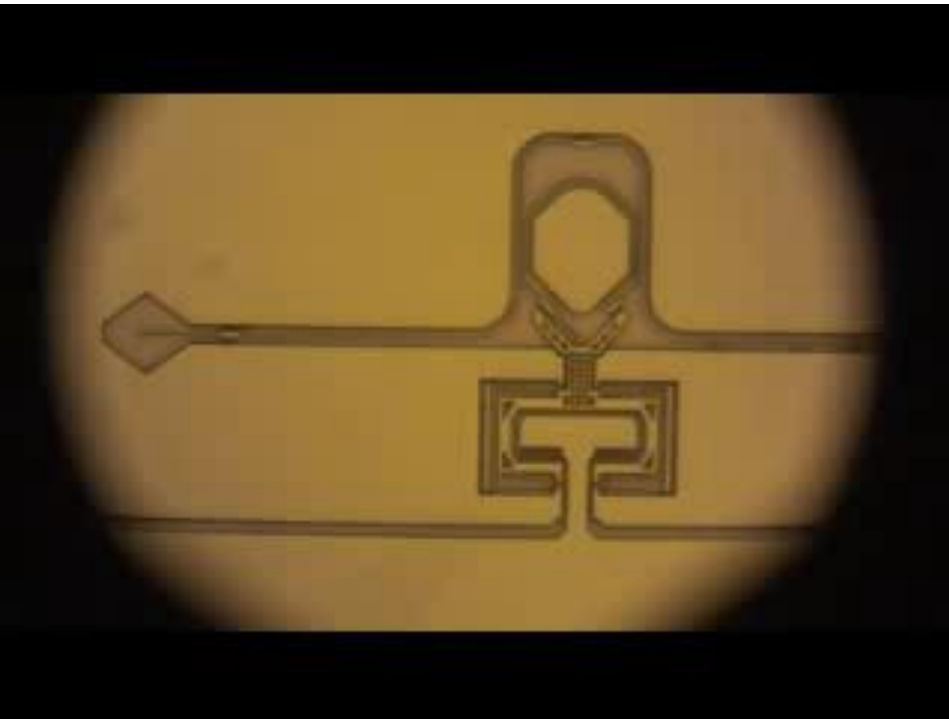
M-series: 12 bits,
13.6mm wide line

Fabricated MZI



Optical measurement

Optical image



Infrared signal image



↑
Through port

↑
Drop port

- $1\mu\text{m}$ displacement at 31V
- Mechanical resonant frequency: 197.8kHz (Wide type), 212.4kHz (Narrow type)
- $1.5\mu\text{m}$ optical output modulation is observed

曲げモーメント駆動による 焦点可変ミラー

MEMS Deformable Mirrors

Technology and applications of micromachined adaptive mirrors

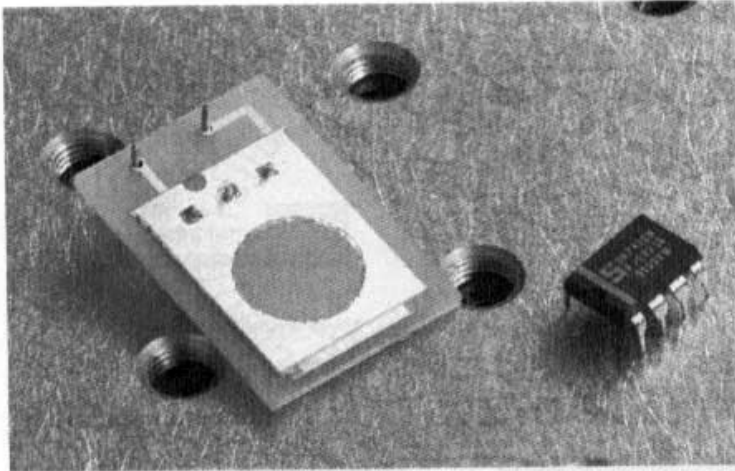


Figure 5. Defocus corrector mounted on a PCB.

or:

$$\varepsilon/\delta a = a/R.$$

From the latter expression, we see that the demands on the shape of the membrane contour are very strict. For example to achieve $\varepsilon = 0.1 \mu\text{m}$ with a membrane mirror having diameter of 1 cm, when the deformed membrane has a focal distance of one meter, the deviation from the circular contour must be less than $20 \mu\text{m}$.

The compensation reported can be applied for the fabrication of more complex shapes, for example for elliptical mirrors for correction of astigmatic beams emitted by semiconductor lasers.

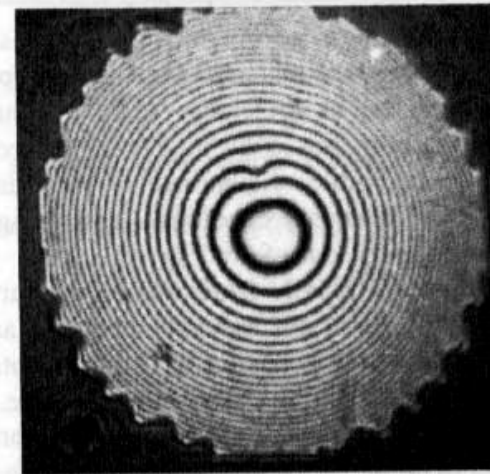
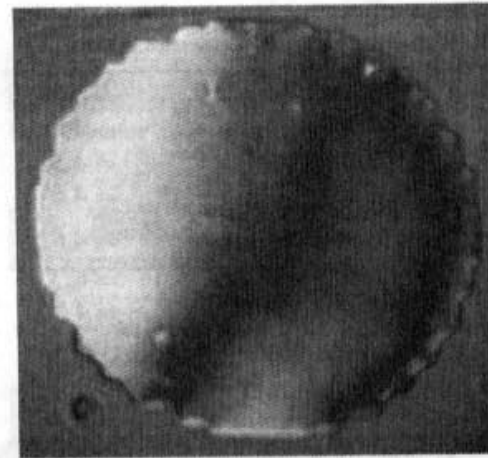
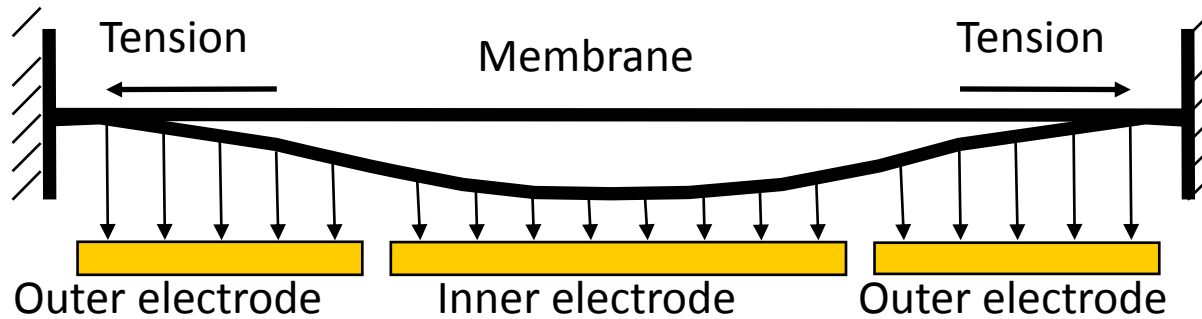


Figure 6. Interferogram of the initial mirror surface with an active diameter of 10 mm (top), the same surface deformed by a control voltage of 90 V, corresponding to a focal distance of 1 m (bottom).

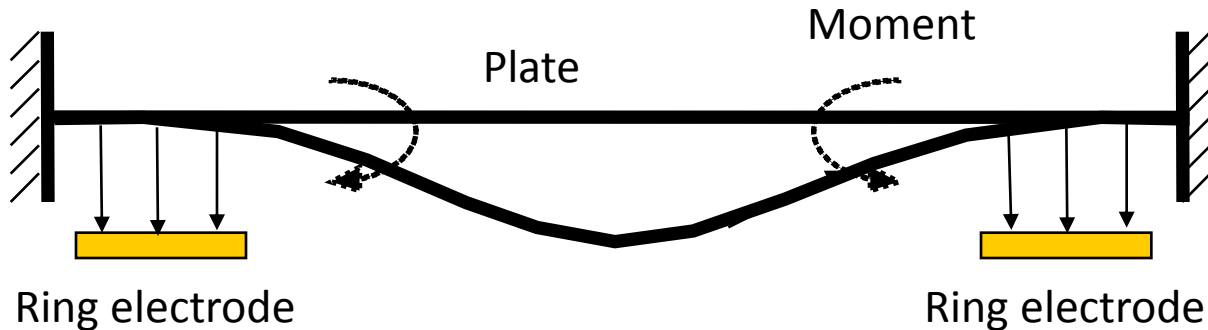
Varifocal mirrors

Membrane mirror



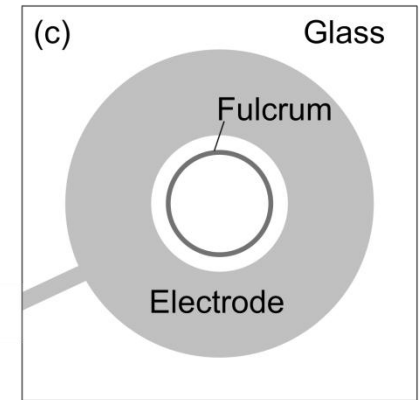
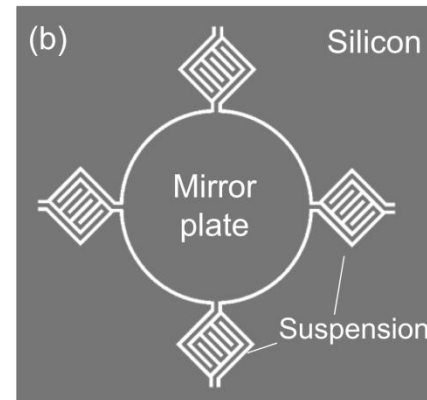
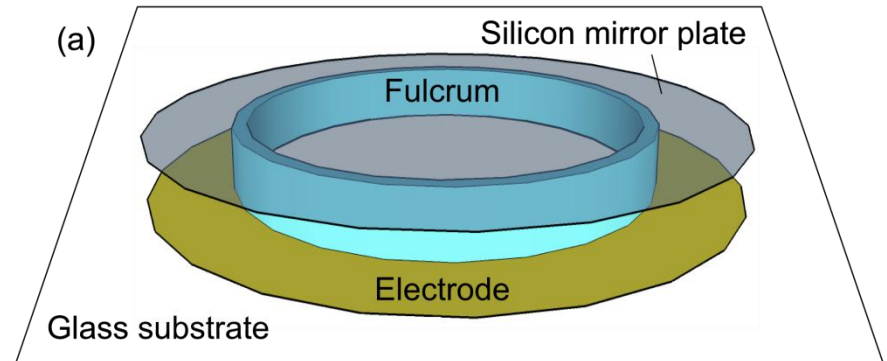
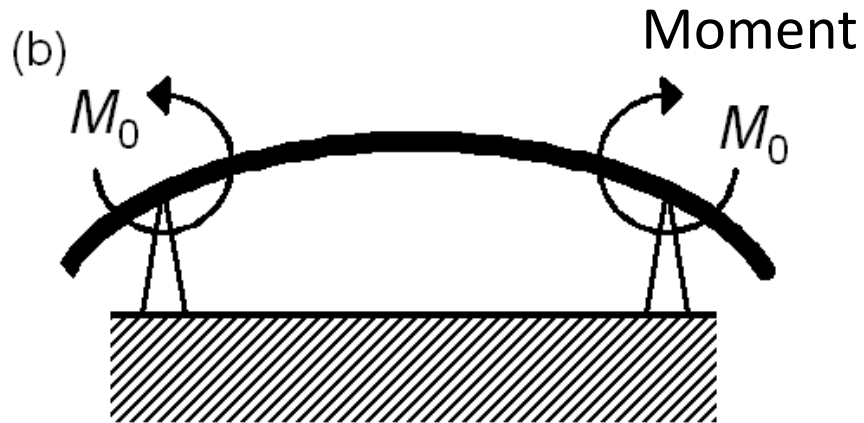
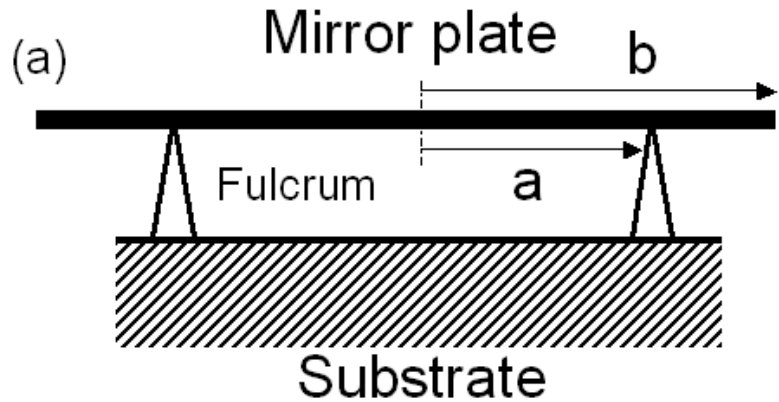
Distributed force is needed to obtain parabolic shape

Plate mirror



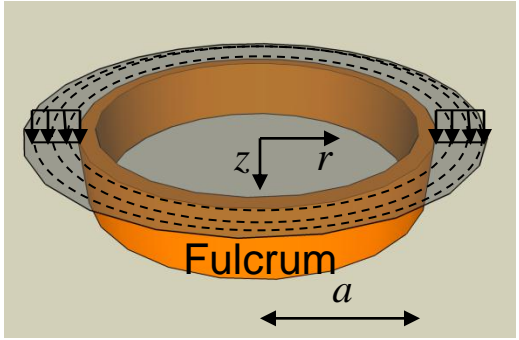
Ring electrode is effective to generate parabolic shape inside the ring electrode
Support conditions affect the region of the parabolic shape

Deformable mirror by bending moment drive



焦点可変ミラーの動作原理

Circular mirror



Ring-shaped load distribution

円板のたわみ曲線の微分方程式 (材料力学)

$$\frac{d^4 z}{dr^4} + \frac{2}{r} \frac{d^3 z}{dr^3} - \frac{1}{r^2} \frac{d^2 z}{dr^2} + \frac{1}{r^3} \frac{dz}{dr} = \frac{P(r)}{D}$$

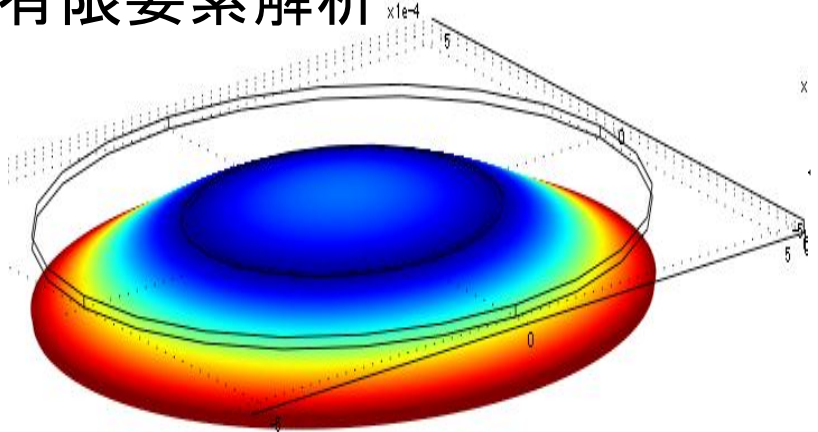
E: Young's modulus
h: mirror thickness
v: Poisson ratio

$P(r)$: Distribution of load, Bending stiffness: $D = \frac{Eh^3}{12(1-\nu^2)}$

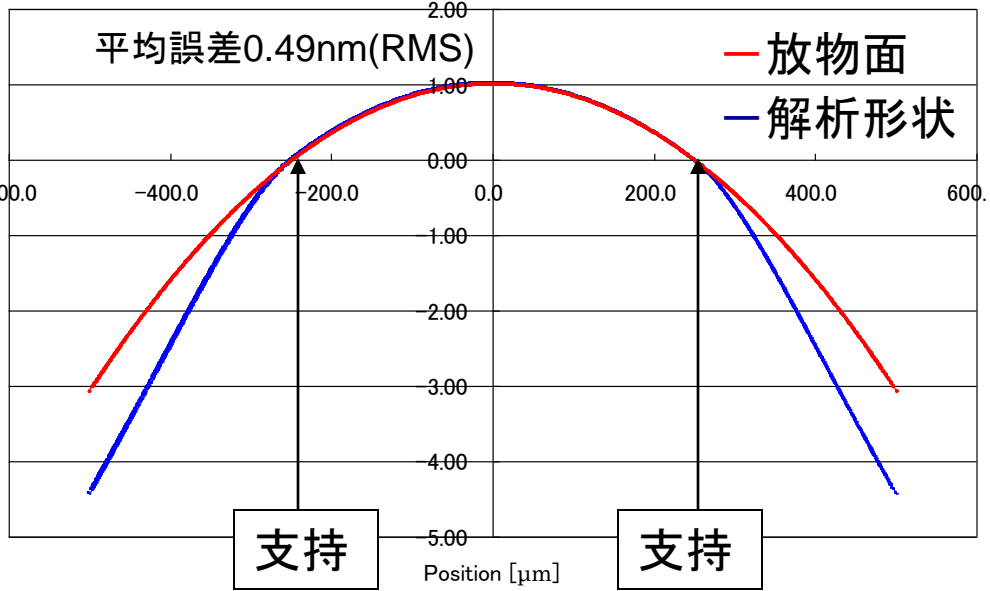
たわみ曲線の近似解

$$z = \frac{M_0}{2D(1+\nu)} (r^2 - a^2) = \frac{6(1-\nu)M_0}{Eh^3} (r^2 - a^2) \quad \text{parabola}$$

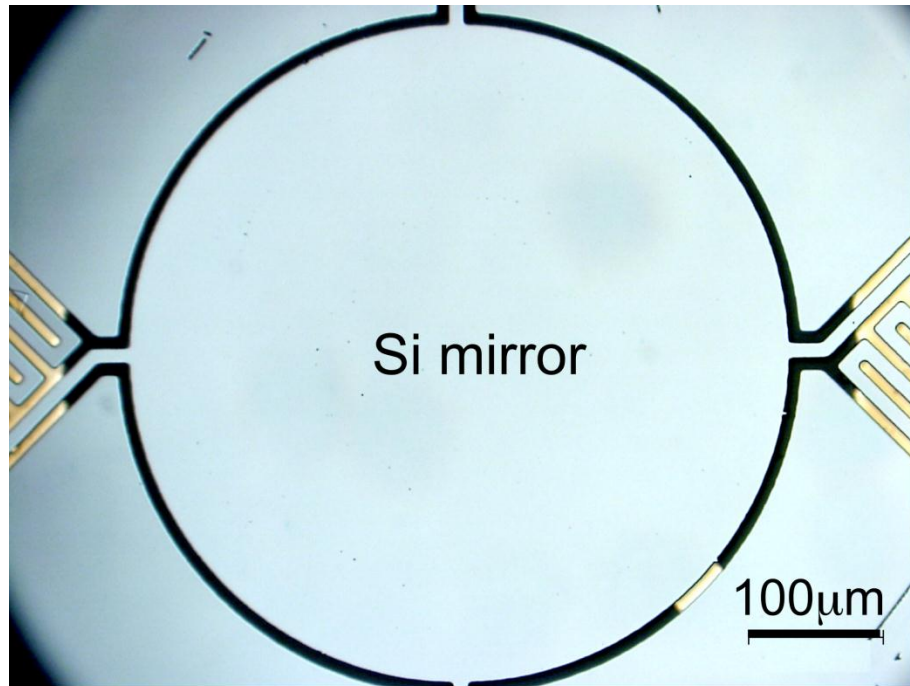
有限要素解析



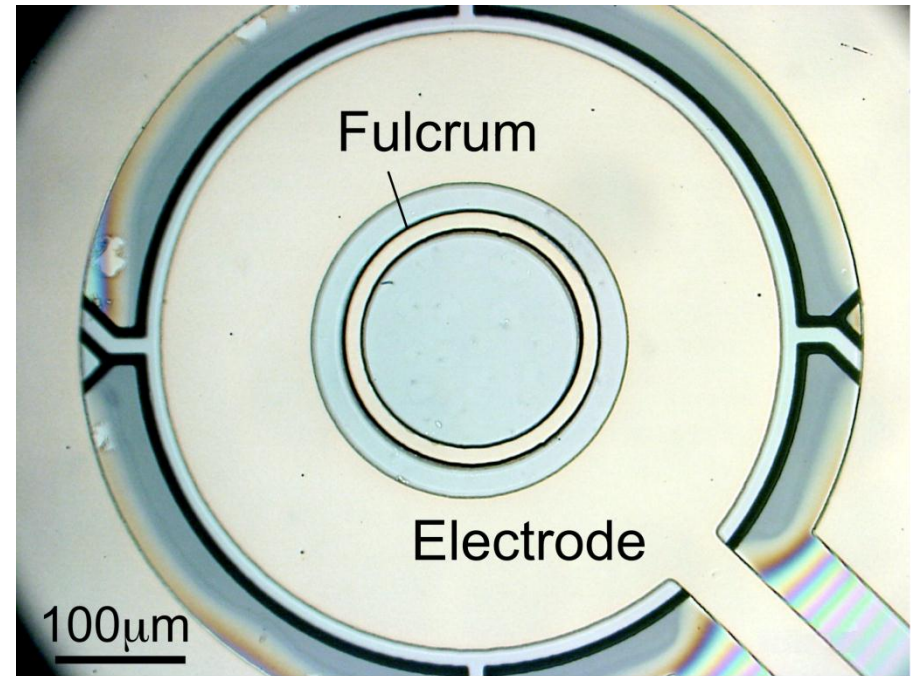
材料: シリコン, 支持外部に分布荷重



Fabricated circular varifocal mirror

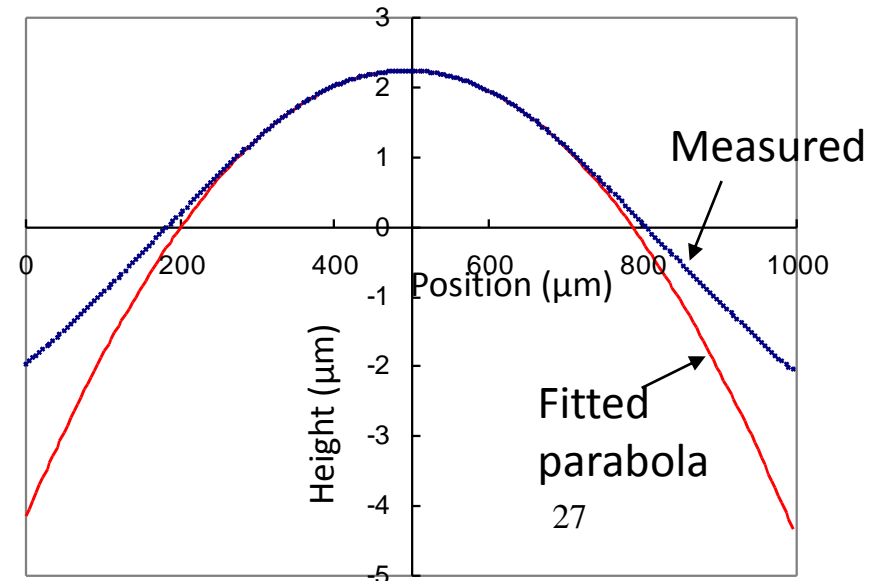
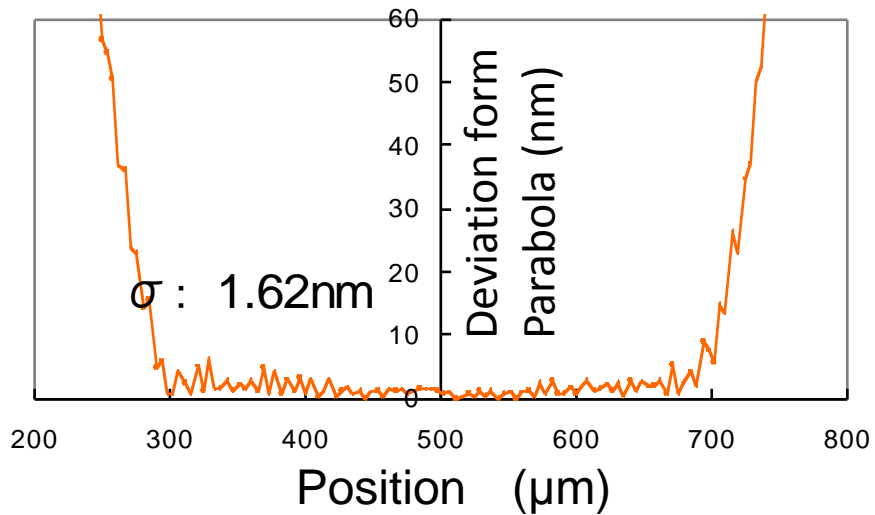
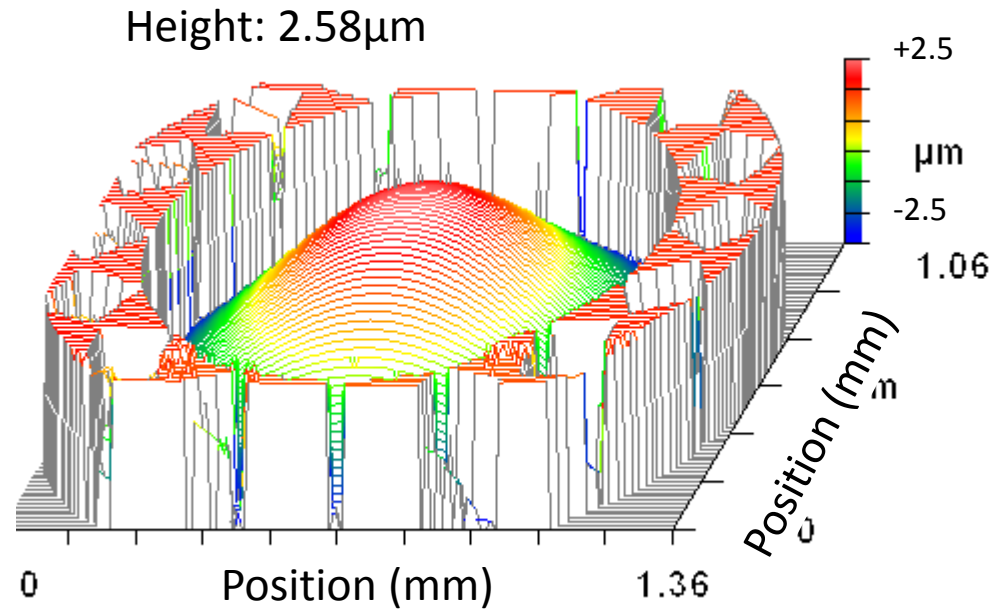
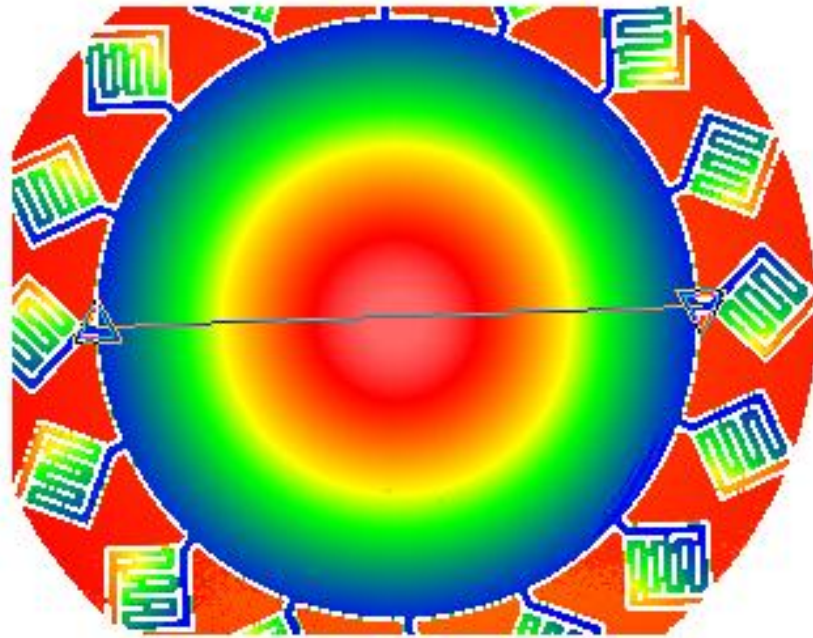


Si mirror side



Glass side

Deformation by voltage

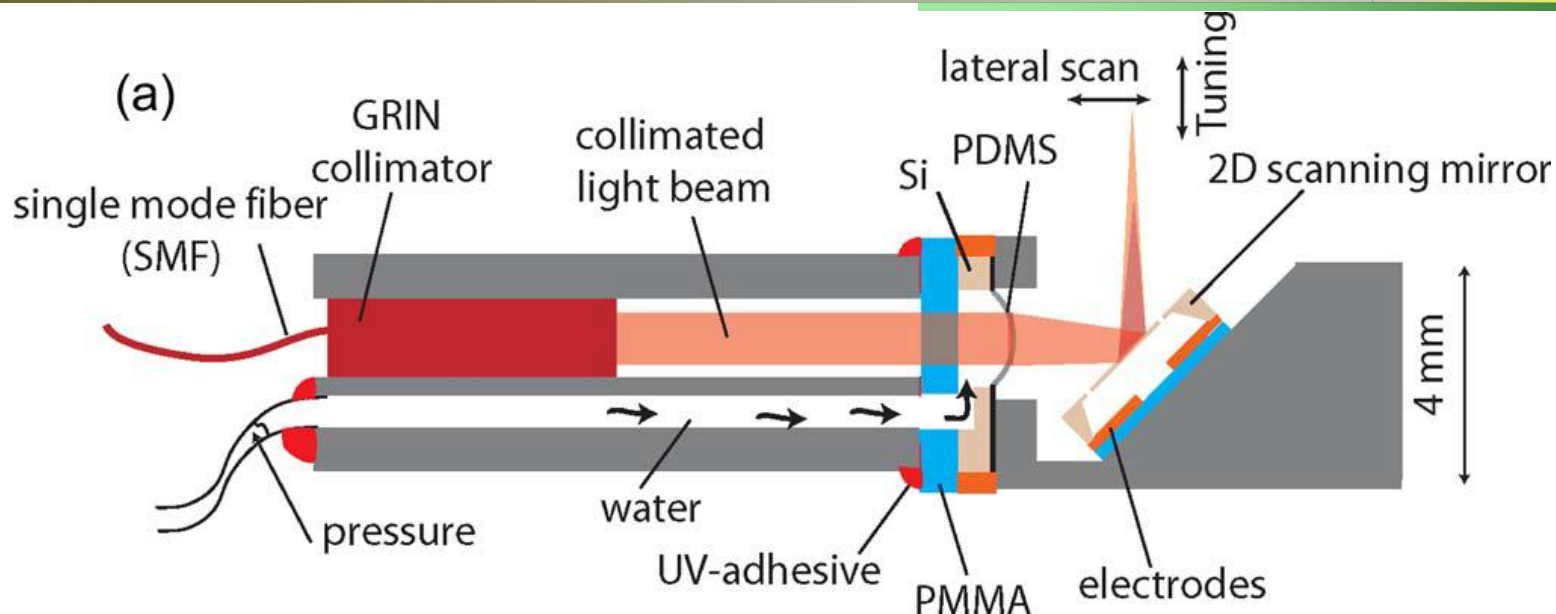


焦点可変ミラーの動作



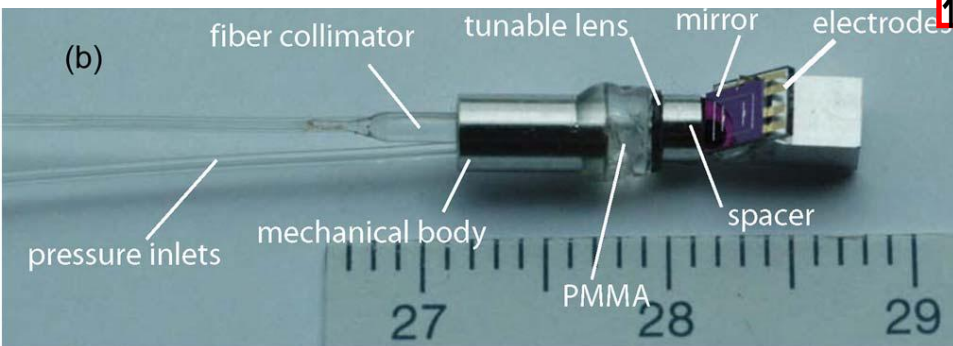
焦点可変ミラーを備えた光スキャナー

焦点可変と光走査機能を搭載した内視鏡

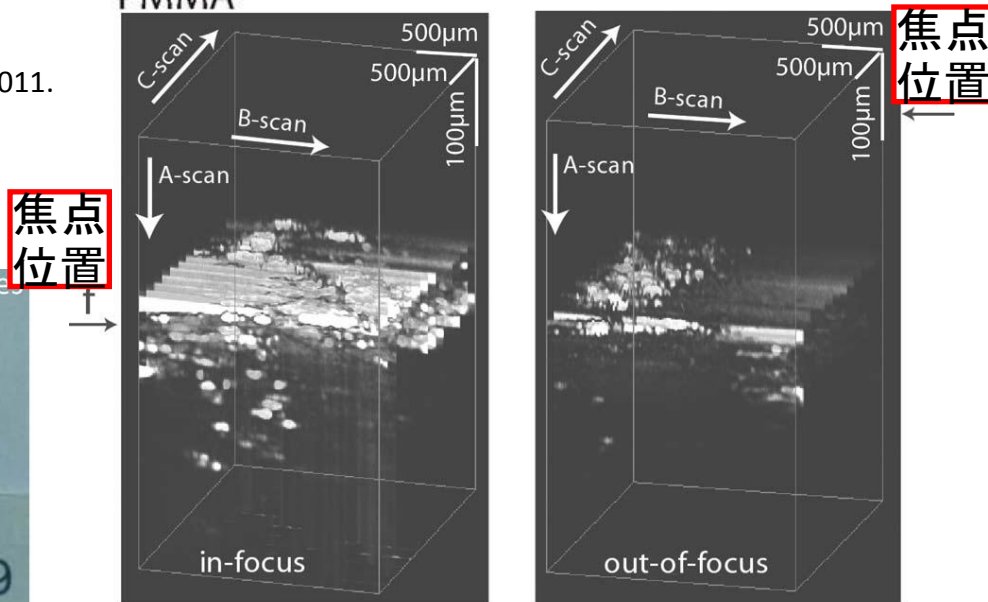


K. Aljaseem et al., IEEE J. Microelectromech. Syst., 20, pp.1462–1472, 2011.

焦点可変と光走査は内視鏡用途で良い画像を得るために必要な機能であることが示されている。

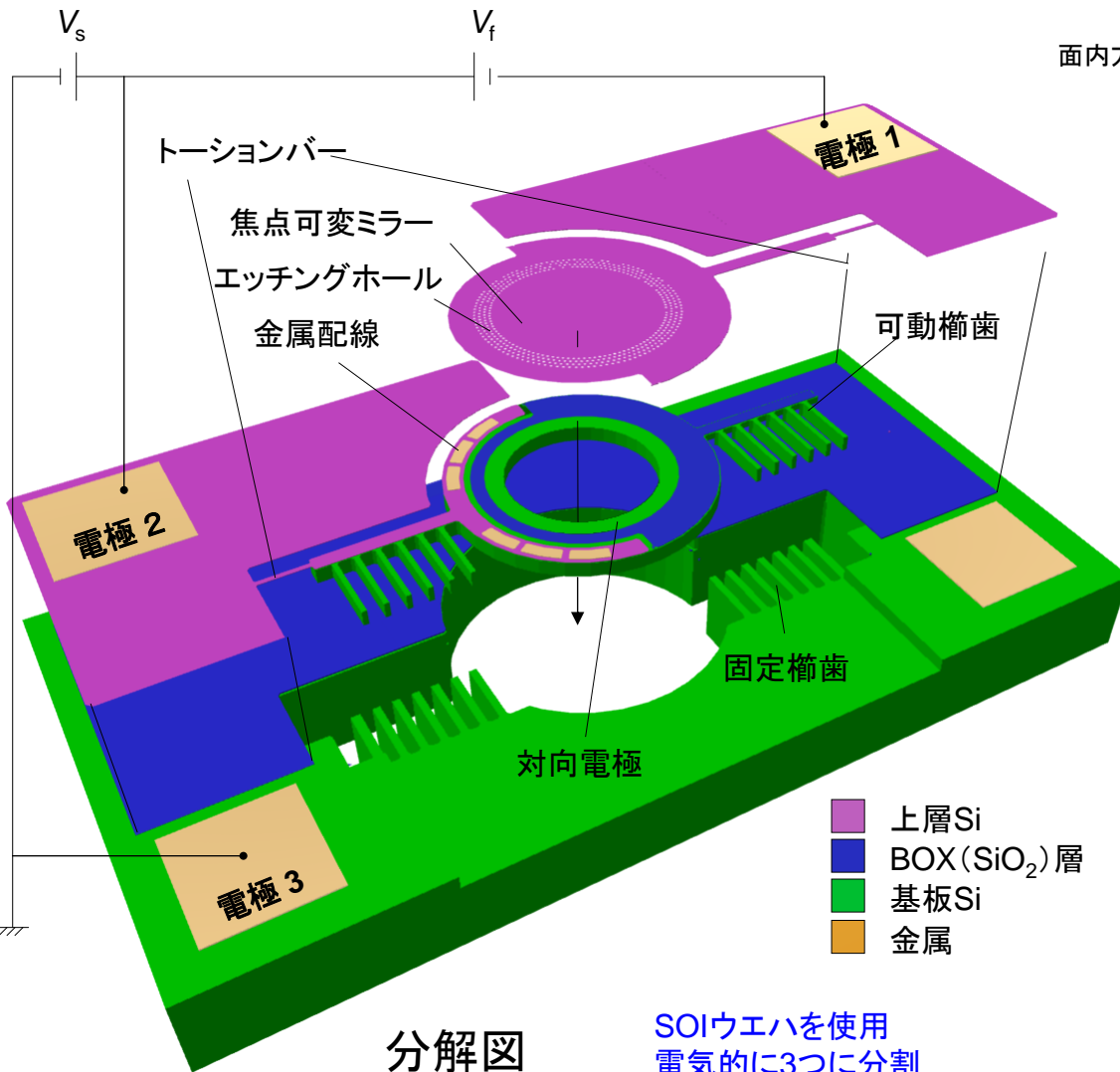


写真

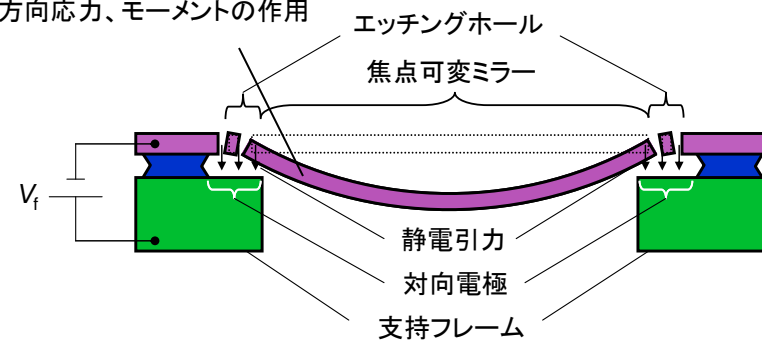


(a) ねぎの皮のOCT画像

提案する焦点可変走査ミラーの構造

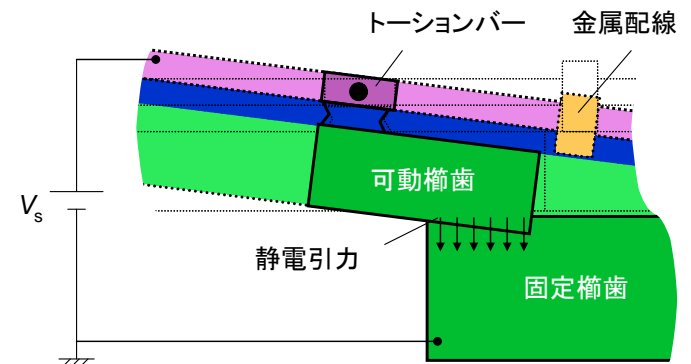


面内方向応力、モーメントの作用



焦点可変ミラーの断面図

焦点可変電圧 V_f の印加によりミラー変形

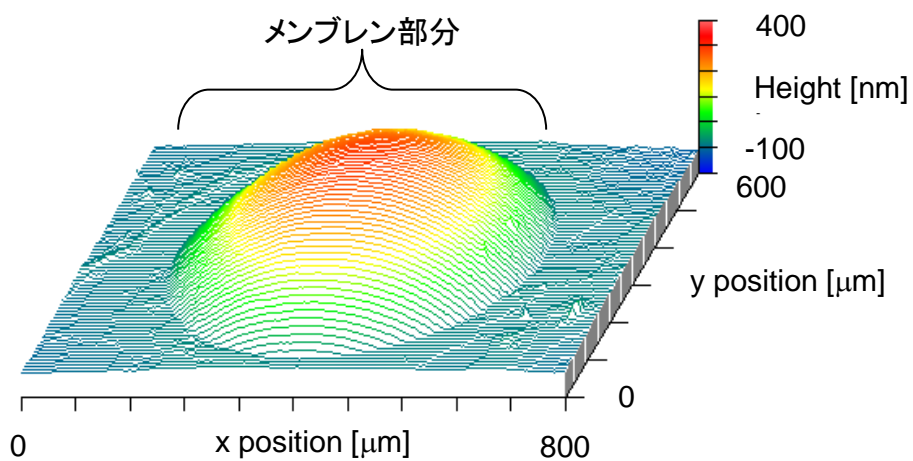
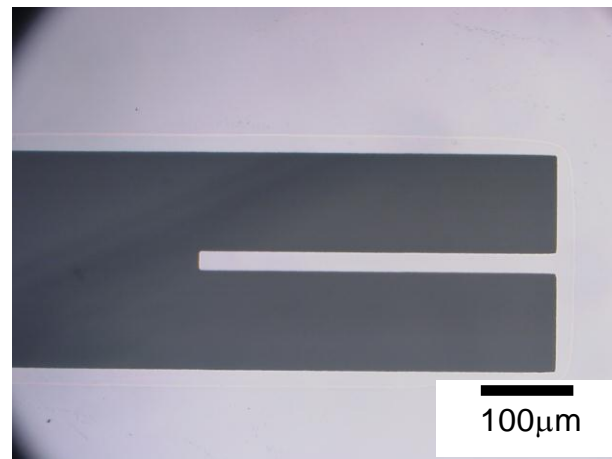
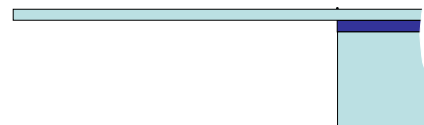
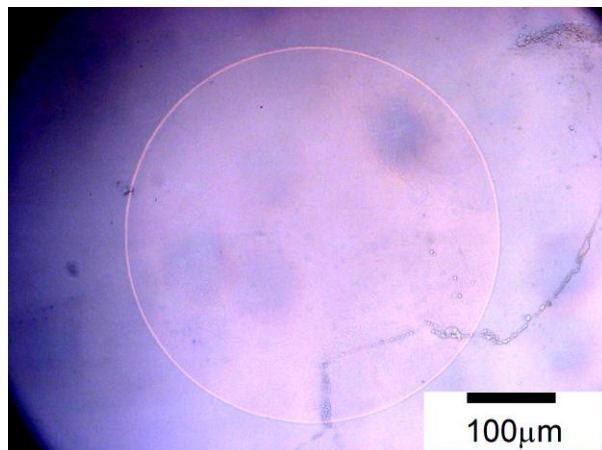


スキャナアクチュエータの断面図

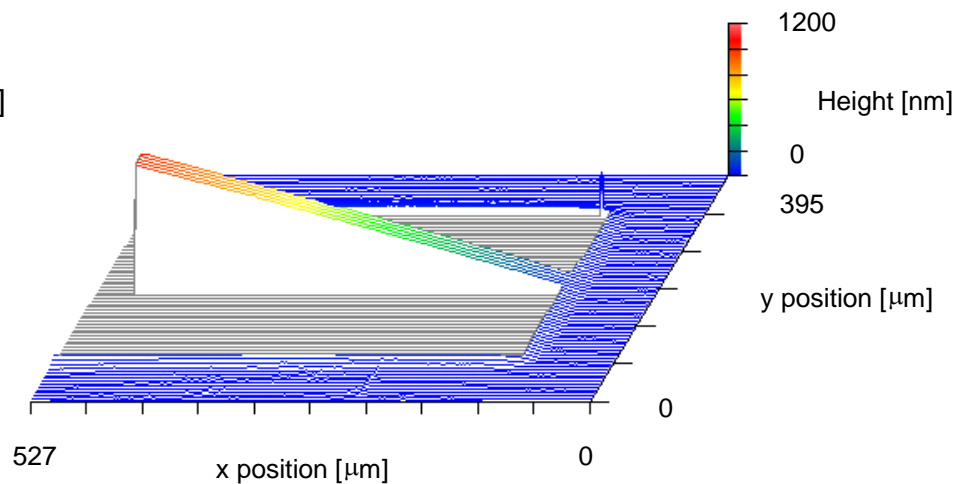
スキャナ電圧 V_s の印加によりミラー回転

スキャナと焦点可変ミラーの機能が集積されている。

円形薄膜ミラーとカンチレバーの形状

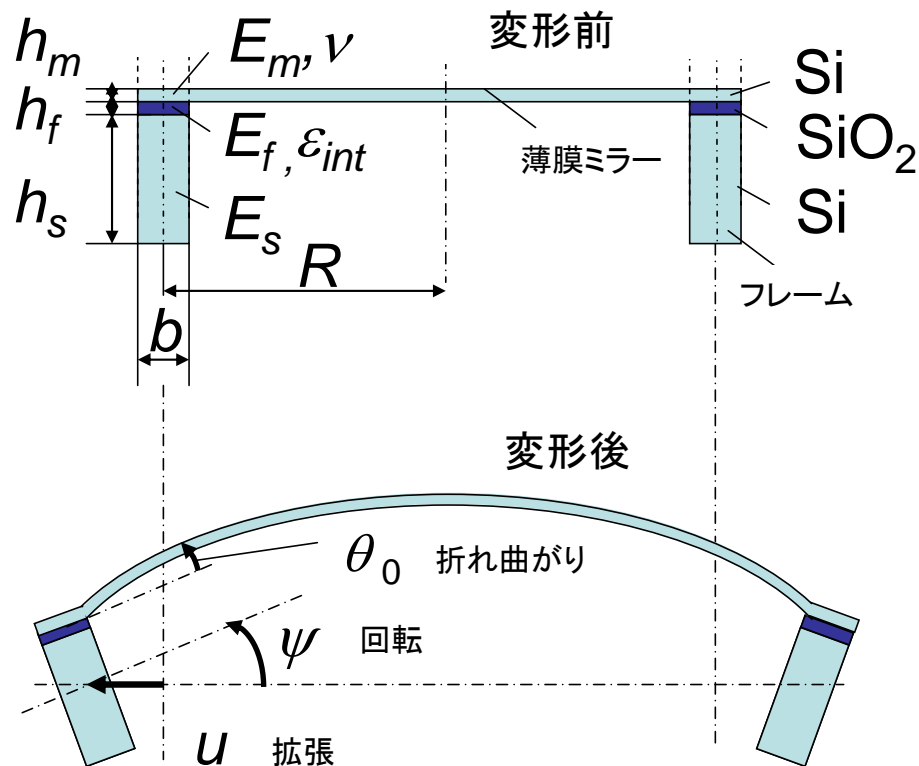


円形薄膜ミラーの形状



カンチレバーの形状

応力による変形の計算



薄膜ミラー断面図

フレーム変形による薄膜ミラー支持条件変化

支持角度	→ 増
面内方向応力	→ 増

フレーム変形の計算結果

拡張変形

$$u_{r=R-\frac{b}{2}} = \frac{-h_f E_f \varepsilon_{int} - \frac{1}{b(1-\nu)} h_m E_m \lambda}{\frac{1}{R-\frac{b}{2}} (h_f E_f + h_s E_s + h_m E_m) + \frac{1}{b(1-\nu)} h_m E_m}$$

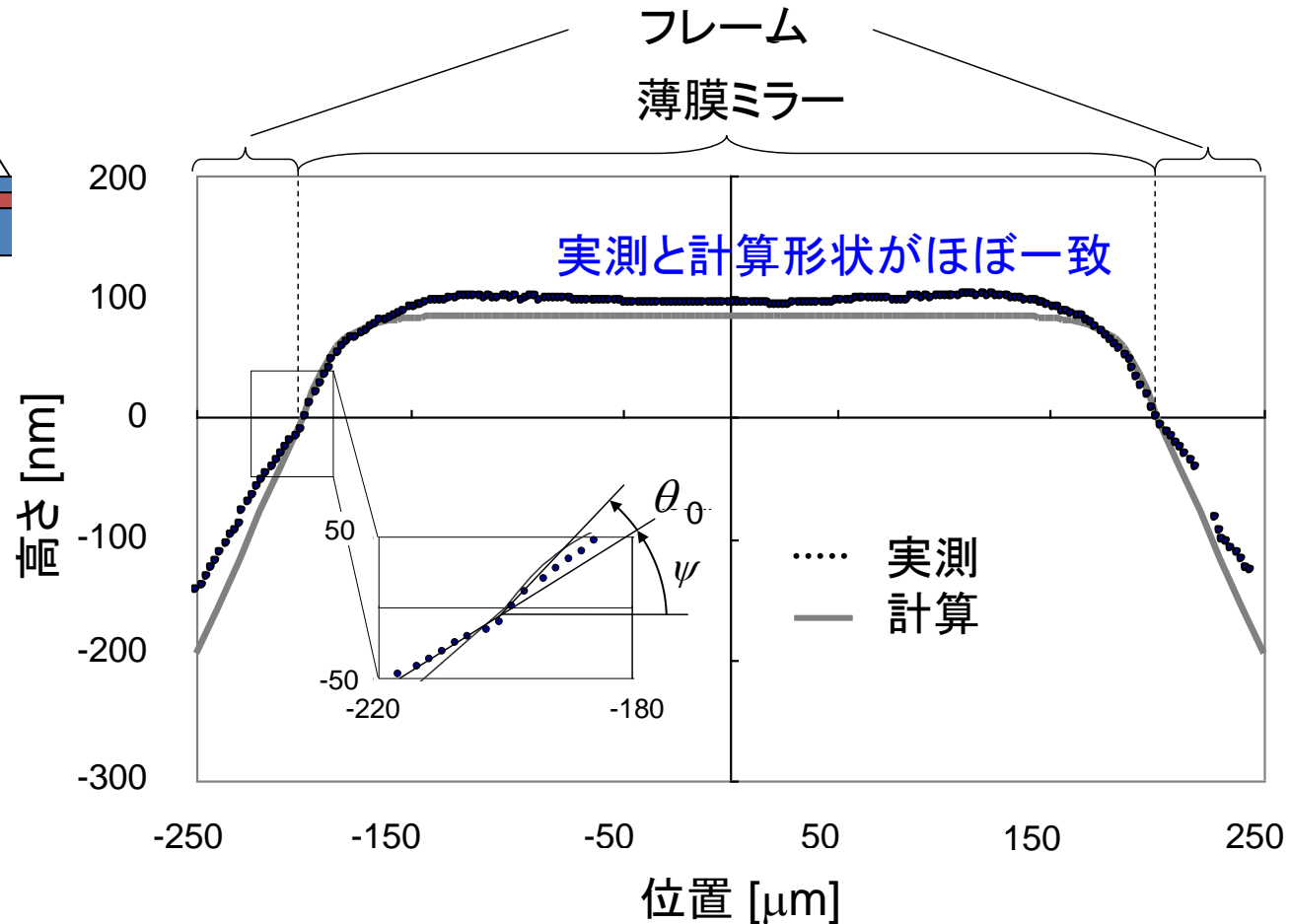
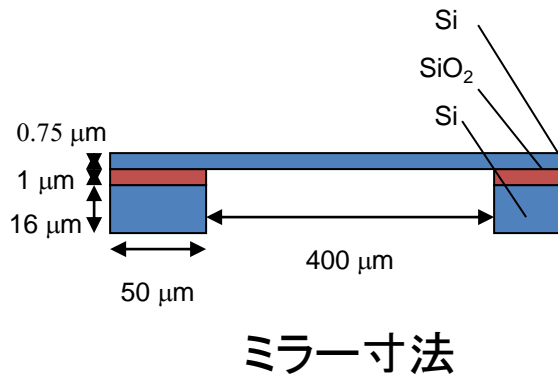
回転変形

$$\psi = - \frac{h_f E_f (\varepsilon_{int} + \varepsilon_a) + h_m E_m \varepsilon_a + h_m \sigma_{m\theta} + \frac{2M_{m\theta}}{bh_s}}{(h_f E_f + h_m E_m) \frac{h_s}{2} + E_s \frac{h_s^2}{6}} R$$

フレーム寸法と面内方向応力の関係

フレーム厚	フレーム幅	面内方向応力
大	小	小
小	大	大

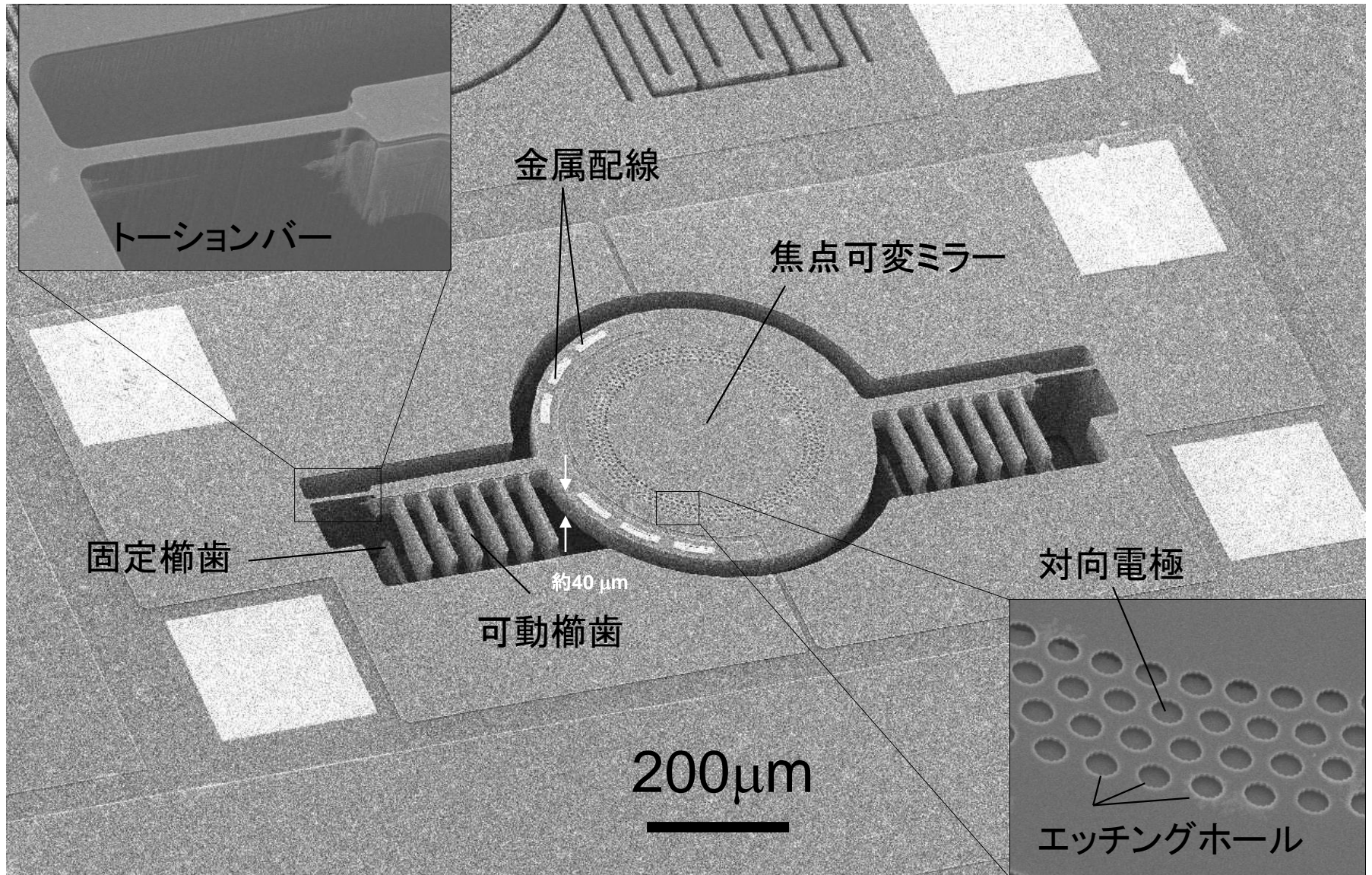
薄膜ミラーの変形の実測と計算結果



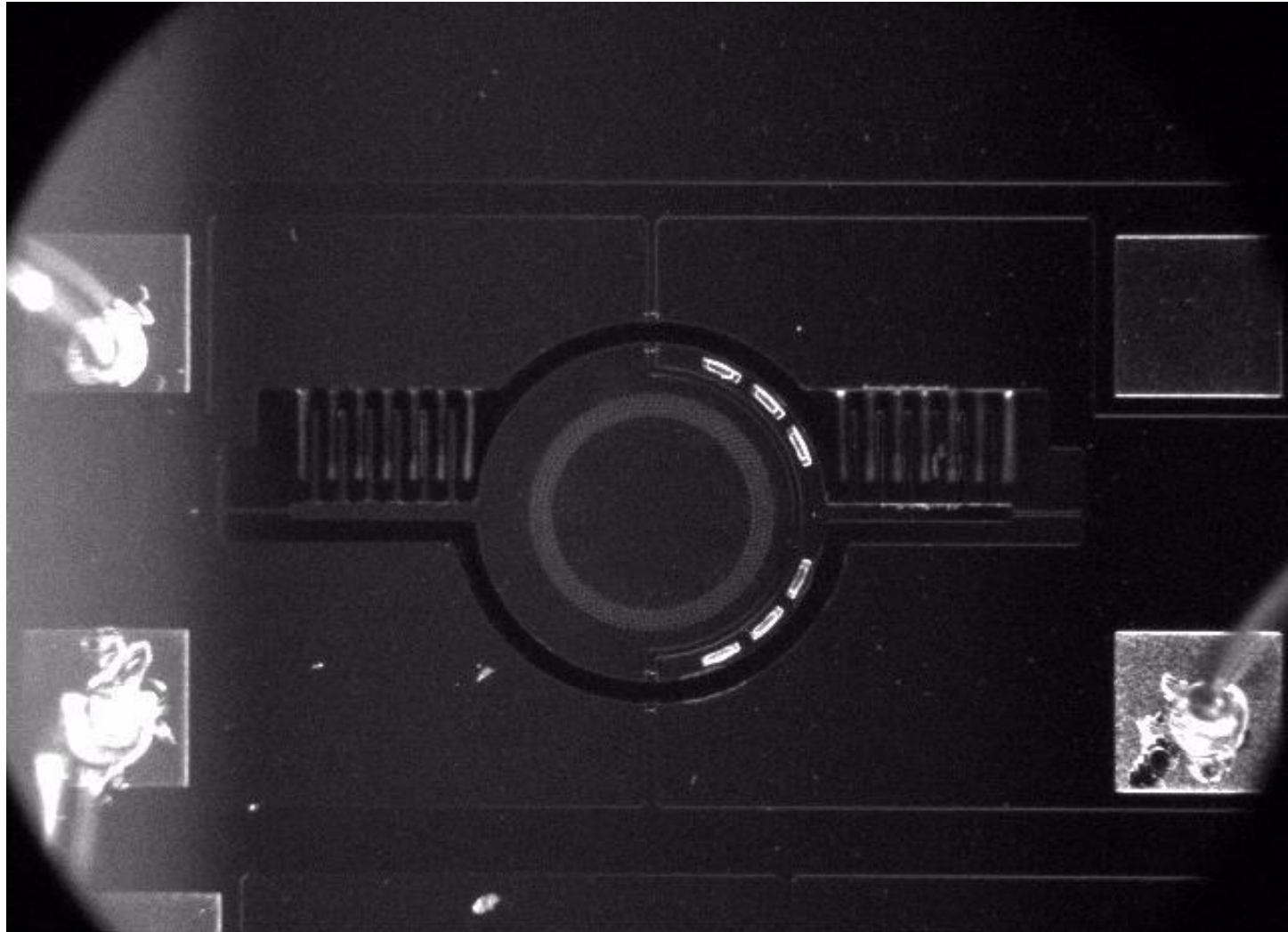
フレーム回転角度 ψ
 ミラー支持部たわみ角 $\psi + \theta_0$
 ミラー面内方向応力 σ_0

測定結果	計算結果
2.8 mrad	3.9 mrad
4.7 mrad	6.2 mrad
20 MPa	47 MPa

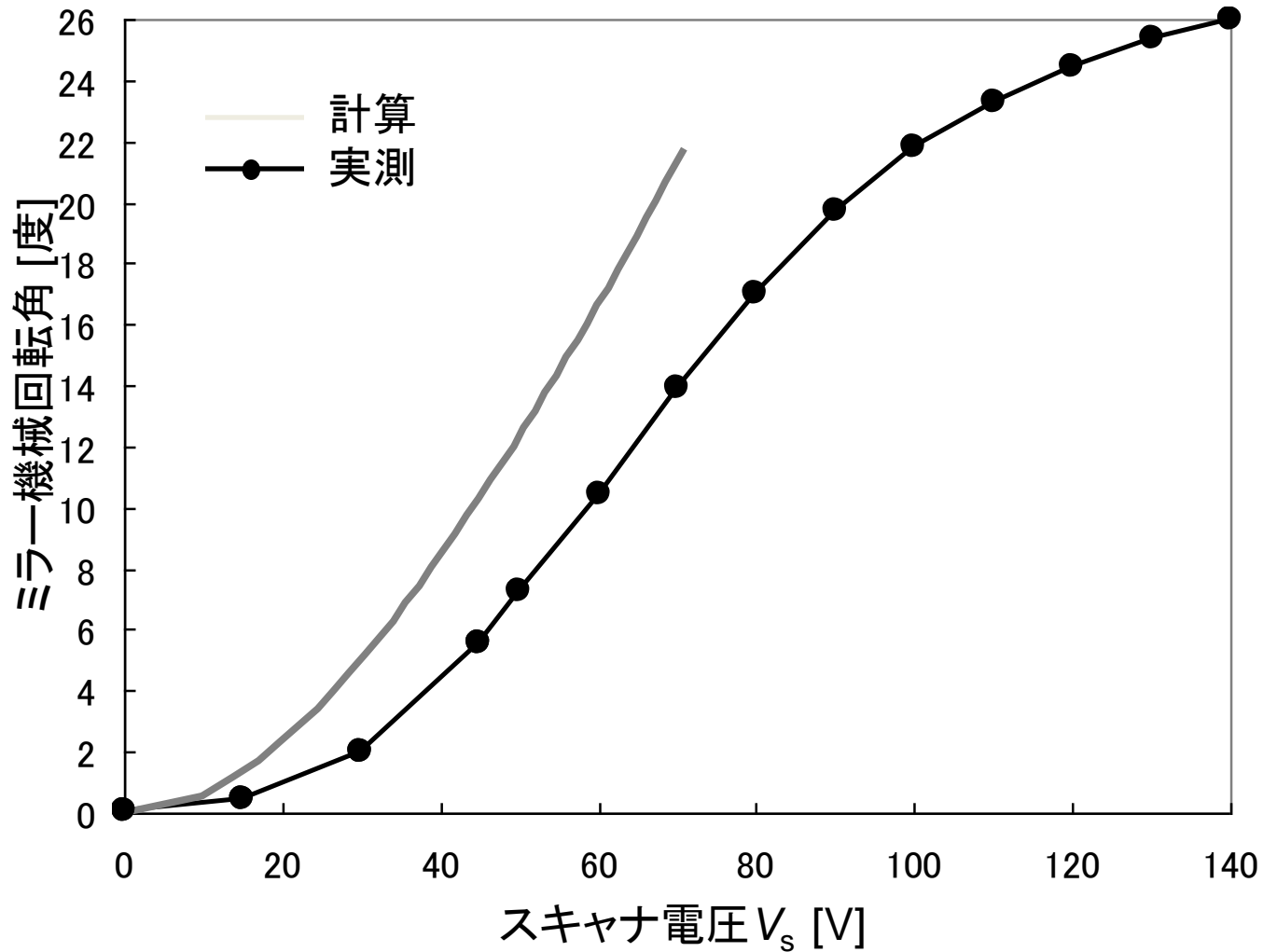
製作したデバイスのSEM写真



スキヤナの駆動動画



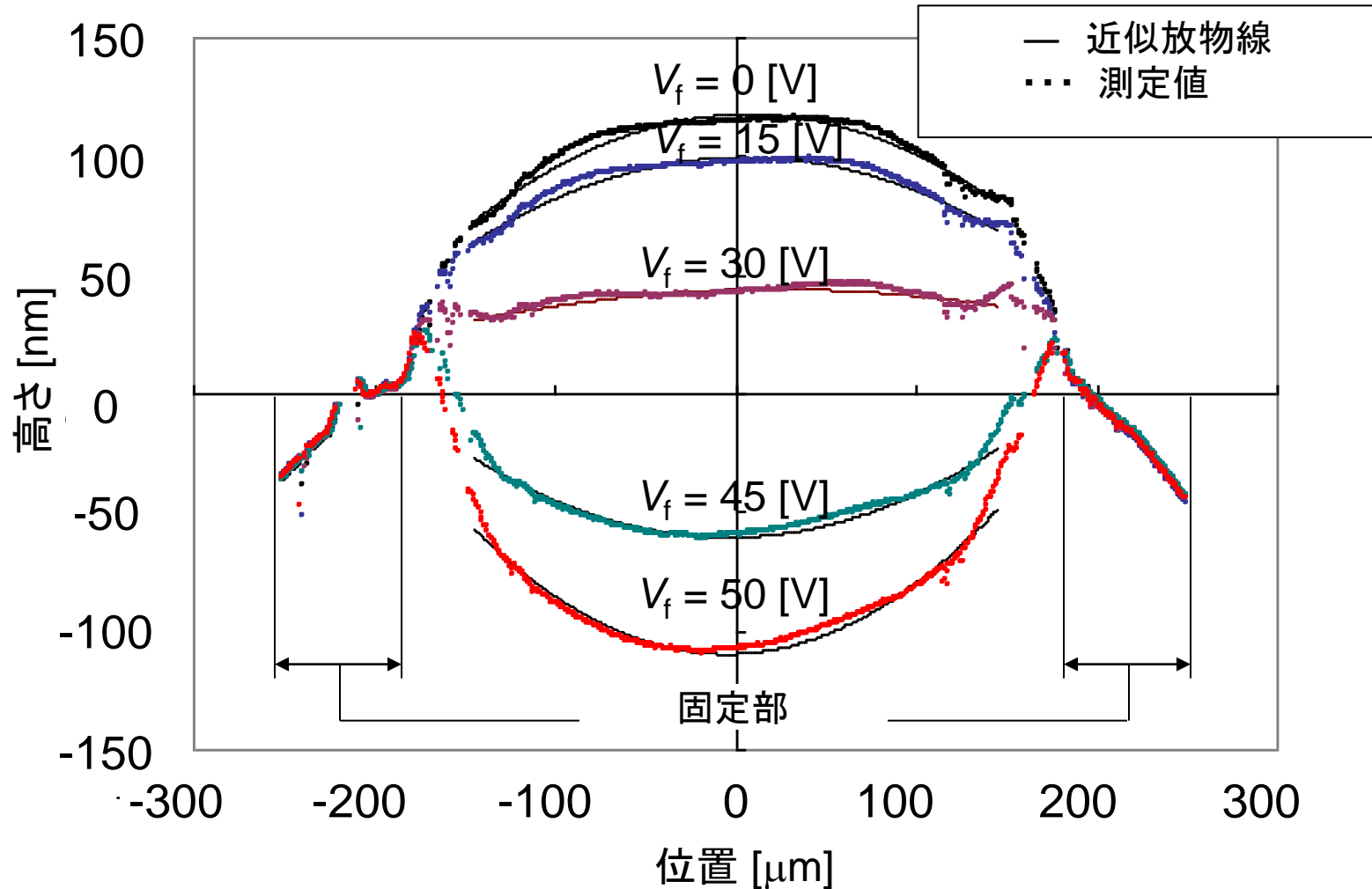
スキヤナの静特性



スキャナ電圧 V_s に対する回転角

140 Vの電圧印加でも電氣的ショートや櫛歯のプルインが発生することなく26度回転⁸⁷した。

焦点可変ミラーの変形特性

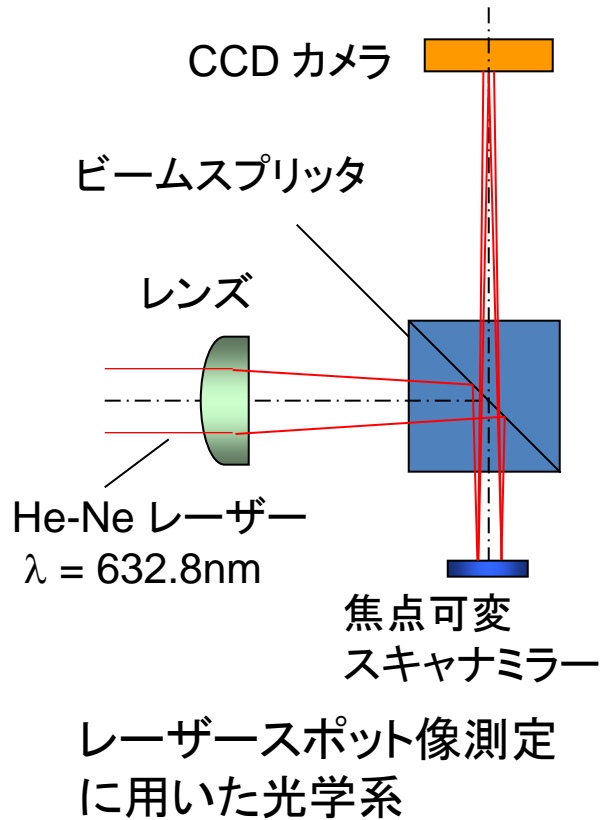


各焦点可変電圧 V_f における焦点可変ミラーの断面形状

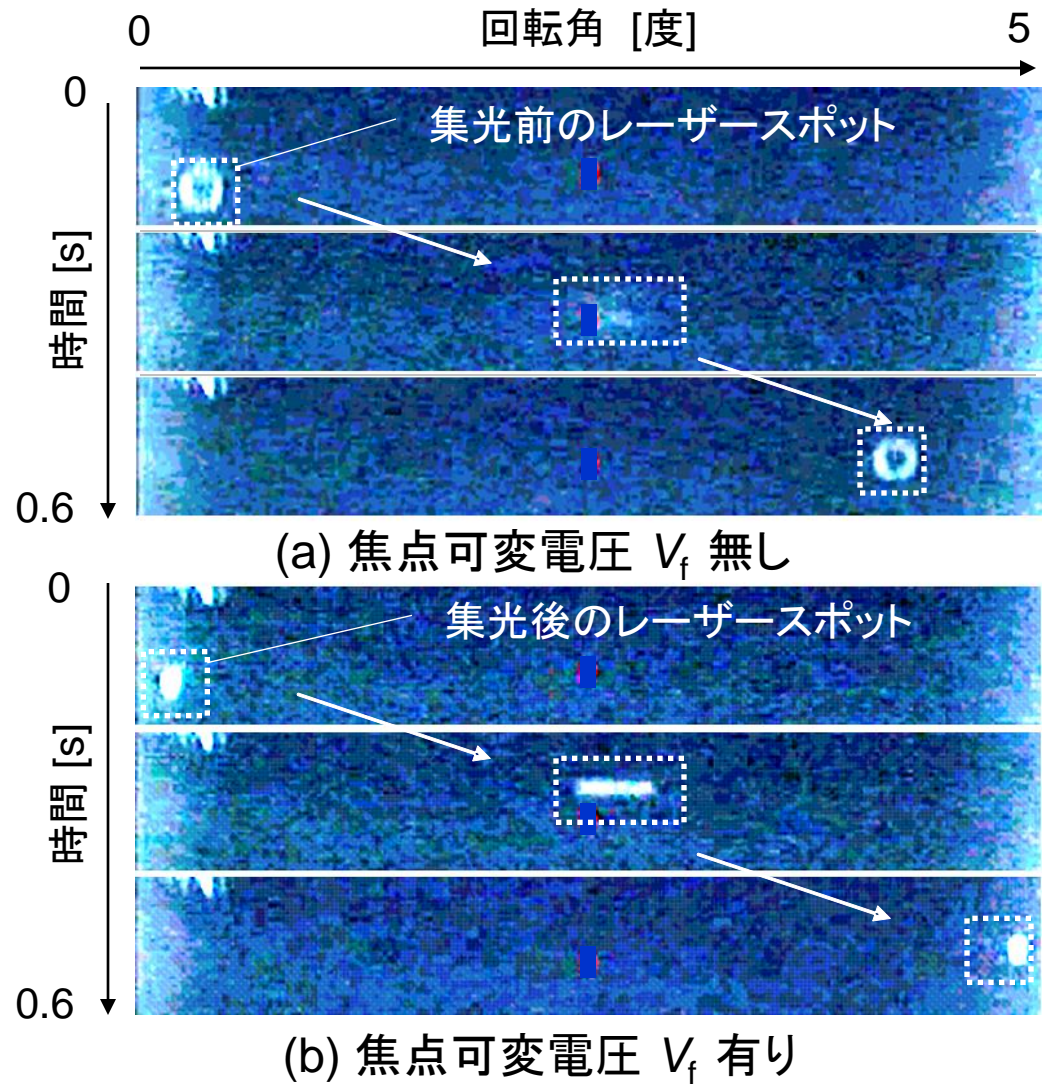
電圧印加と共に徐々に凹面形状に変形した。

座屈変形のような不安定な動作や、電気的なショートは観測されなかった。

焦点と走査の同時駆動実験



スキャナと焦点可変ミラーの駆動によりレーザ光走査と集光を同時にできることを確認した。



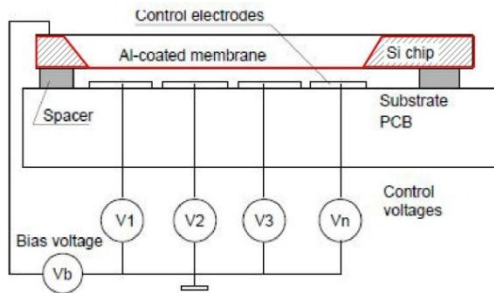
スキャナと焦点可変ミラーの同時駆動時のビーム走査像

波面補償デフォーマブルミラーの製作

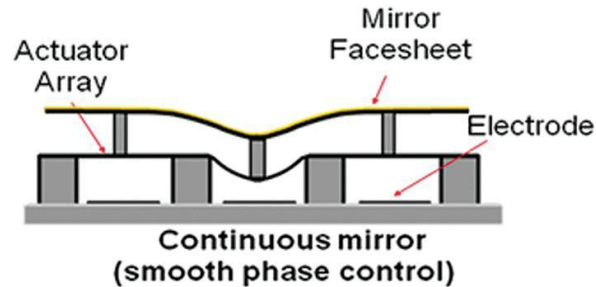
Introduction – MEMS-DM Development-

Single Membrane

OKO

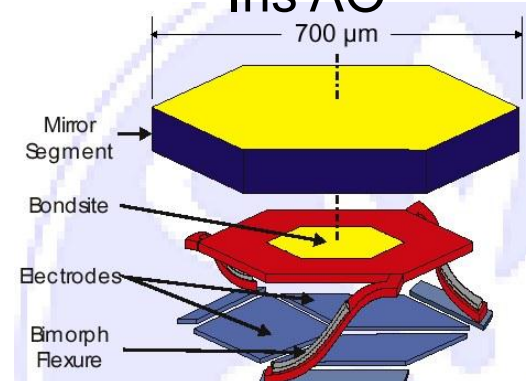


lamineate Membrane Boston Micromachines



Segmented

Iris AO



Element count < 100
Stroke > 10 μm (center)
Small stroke at edge
Element count not enough

Element count < 4096
Stroke not enough (< 5 μm)

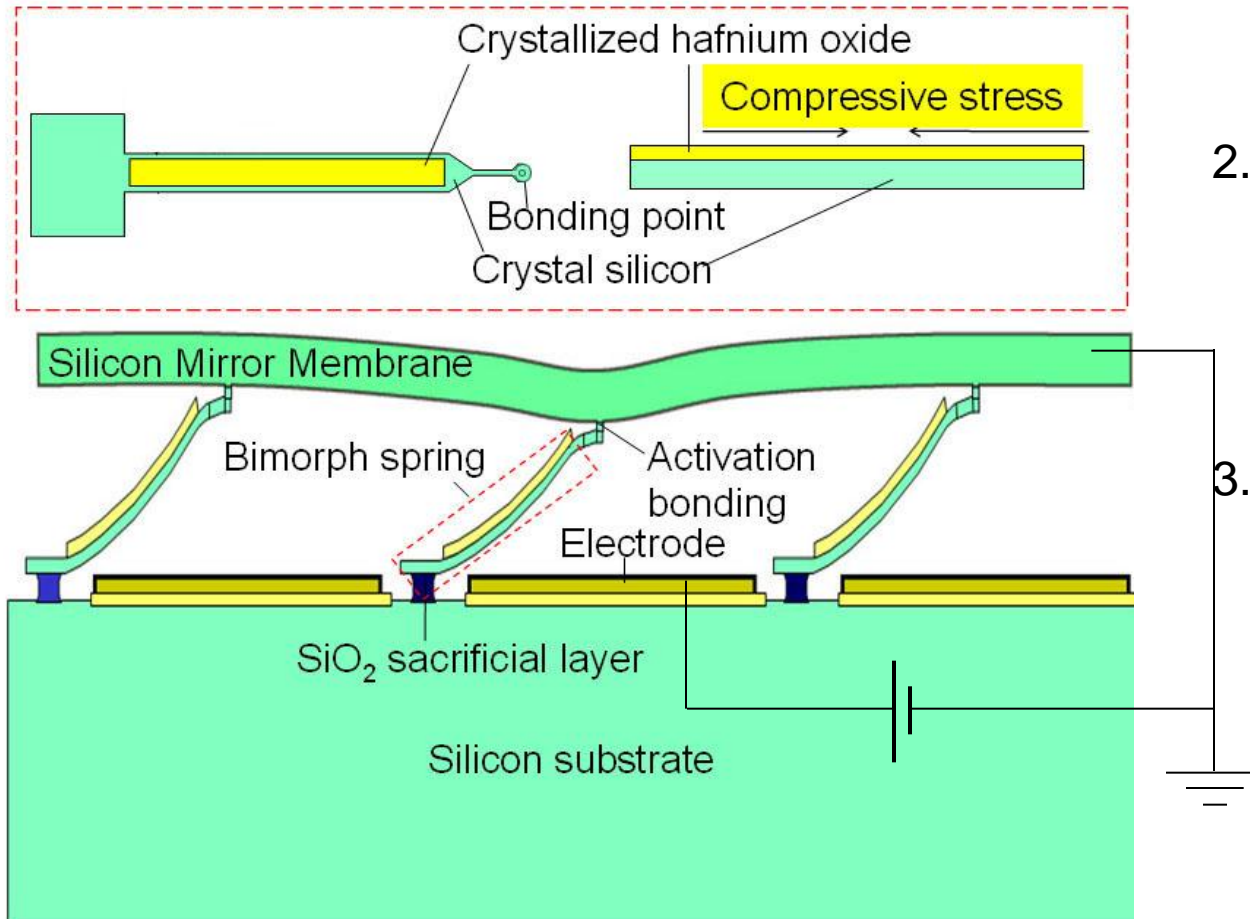
Element count > 100
Stroke > 10 μm
Diffraction occurs at the pitch between the segmented mirrors

The stroke of the electrostatic actuated DM is usually limited by the **air gap** between the electrodes and the mirror membrane. Air gap is usually generated by

1. Surface micromachining (sacrificial layer deposition → etching) cannot generate a big vertical gap which is **limited** by the thickness of the sacrificial layer.
2. Wafer bonding process can generate a large air gap by bond a mirror membrane to a micro-post array.

MEMS-DM – Main design -

We propose a new structure membrane MEMS-DM by combining wafer bonding process and **Si/HfO₂ Bimorph spring array**

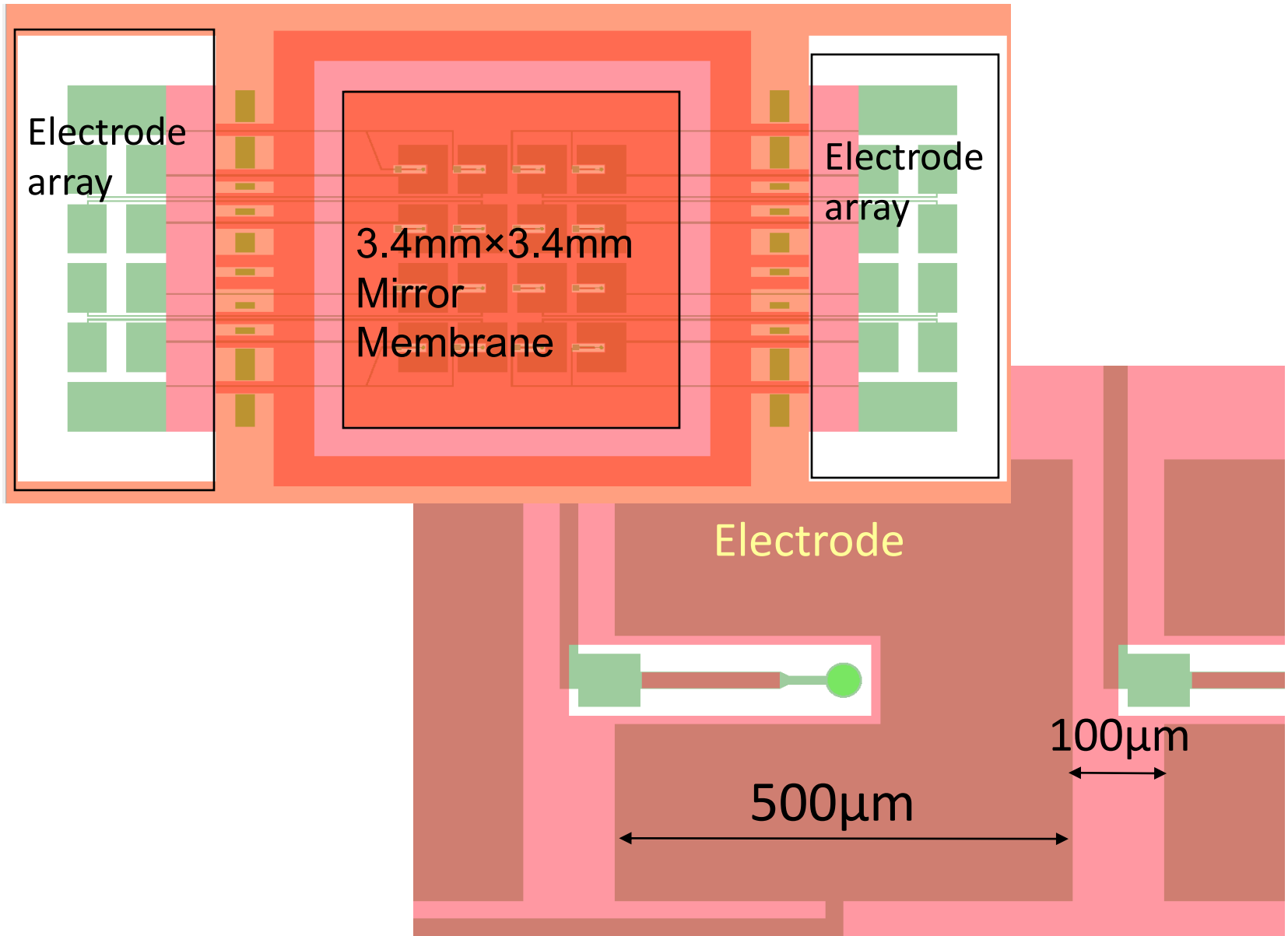


1. HfO₂ **crystallization-induced stress** is used to introduce large air gap.
2. Relatively **soft spring** structure (small spring constant) instead of fixed posts is used to increase the stroke.
3. High optical quality mirror surface is guaranteed by the top layer of SOI wafer and the wafer bonding process.

High-stroke MEMS-DM Structure

MEMS-DM – Design -

3. design overview



MEMS-DM – Design -

1. The dimension of bimorph spring

for MEMS-DM

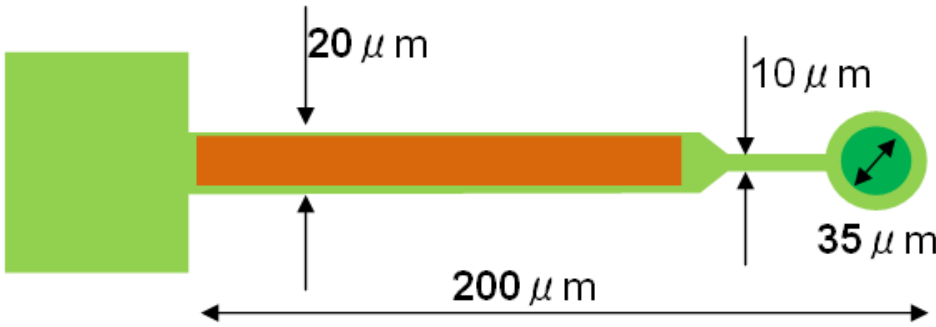
Target stroke: **20 μm**

For the Parallel-plate actuator, it is

demonstrated that range of motion is limited to less than **one third of the initial gap**

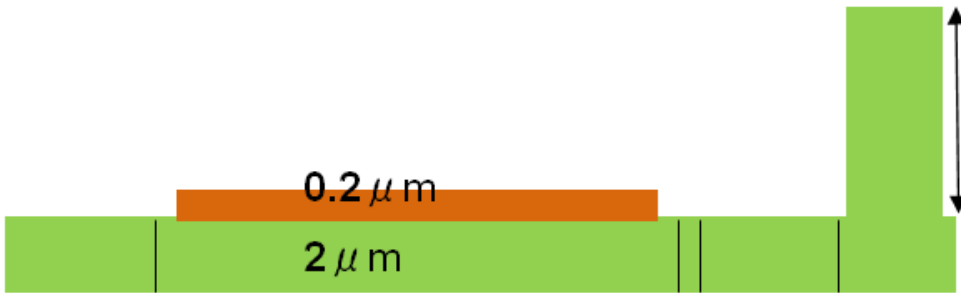
→ **Initial gap > 60 μm**

Length (μm)	Deflection before crystallization (μm)	Deflection After Crystallization (μm)	Film stress of the crystallized HfO_2
100	9.20	33.72	2.11Gpa
200	38.06	131.86	



Out-of-plane Deflection calculated to be :

$$\delta = 48.7 \mu\text{m}$$



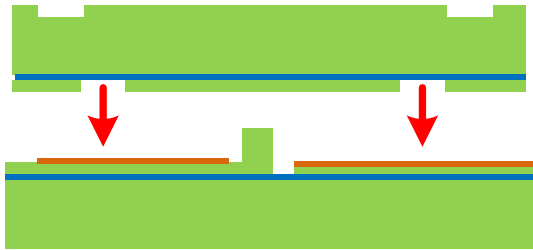
Electrode gap

$$= \delta + 10 \mu\text{m} = 58.7 \mu\text{m}$$



MEMS-DM –Fabrication flow : Bonding and Release

(3-a) Plasma activated bonding



(3-d) SiO₂ Dry Etching (CHF₃)



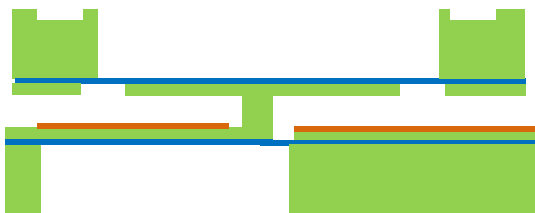
(3-b) Actuator chip handle layer etching



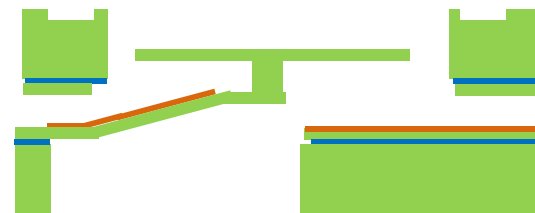
(3-e) SiO₂ Dry Etching (CHF₃)



(3-c) Mirror chip handle layer etching

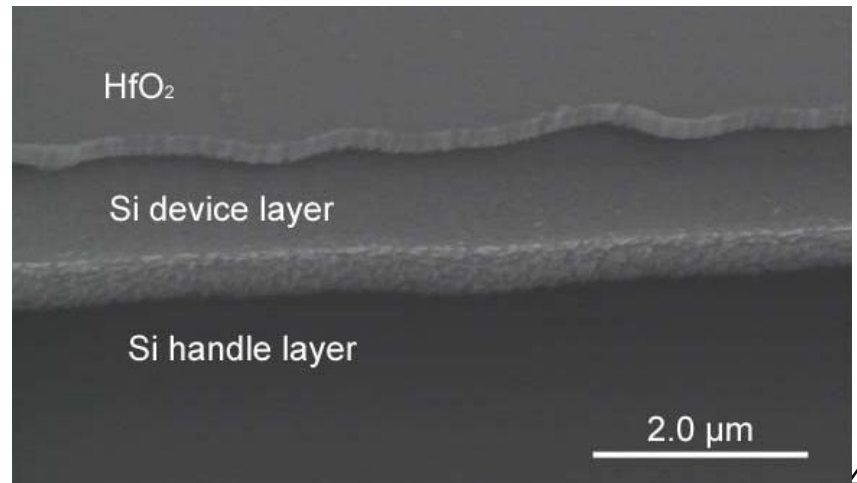
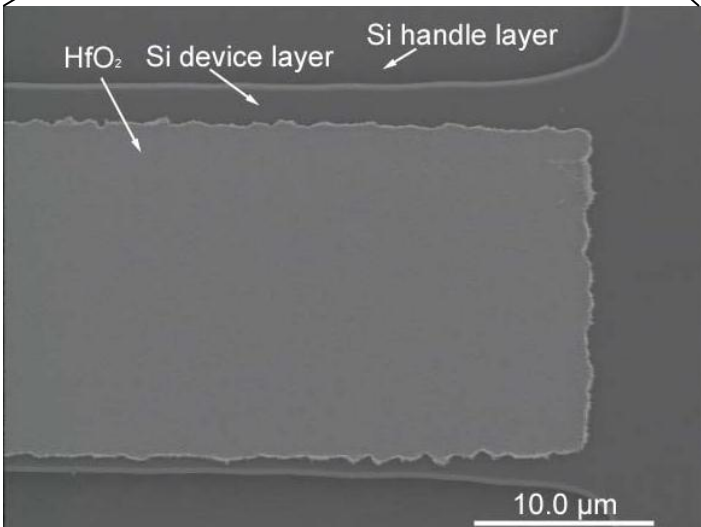
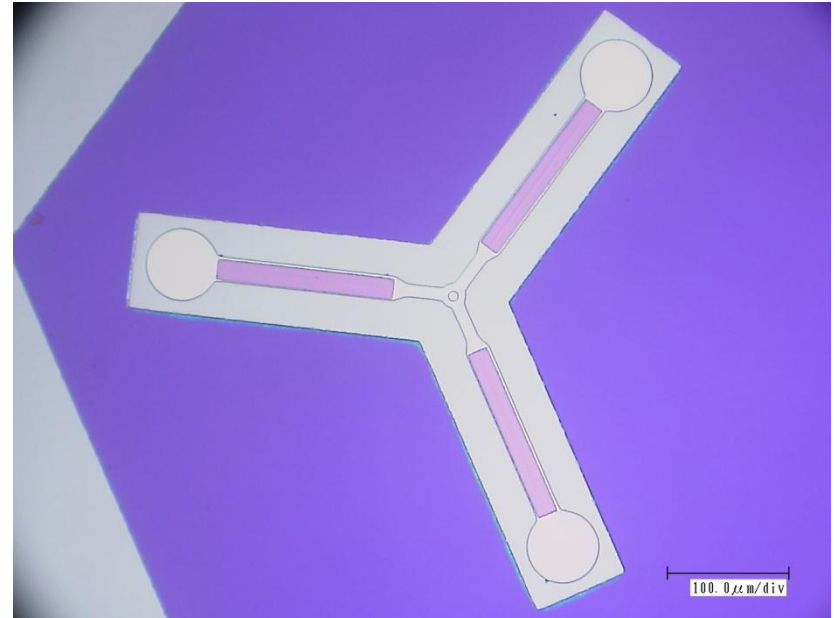
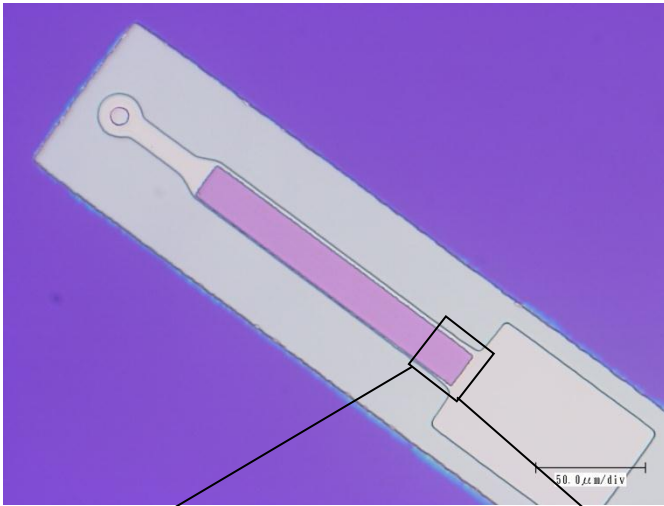


(3-f) Annealing (HfO₂ crystallization)



MEMS-DM –Actuator chip-

Actuator Fabrication: Microphotos & SEM Images

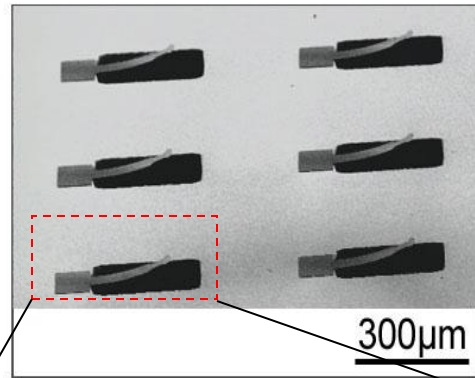


MEMS-DM – Si/HfO₂ Bimorph spring

Fabricated bimorph spring

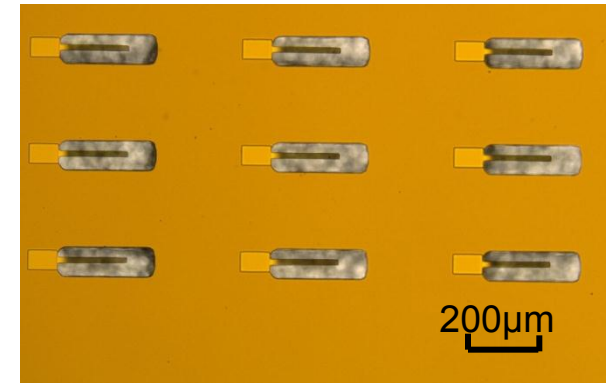
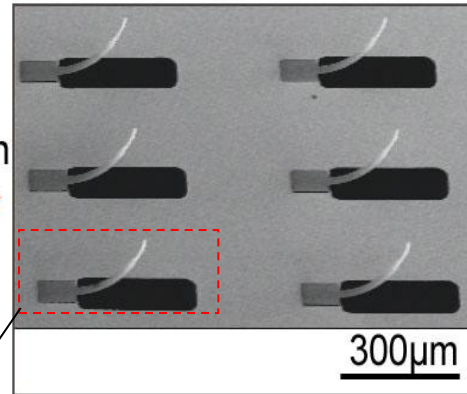


結晶化させる前

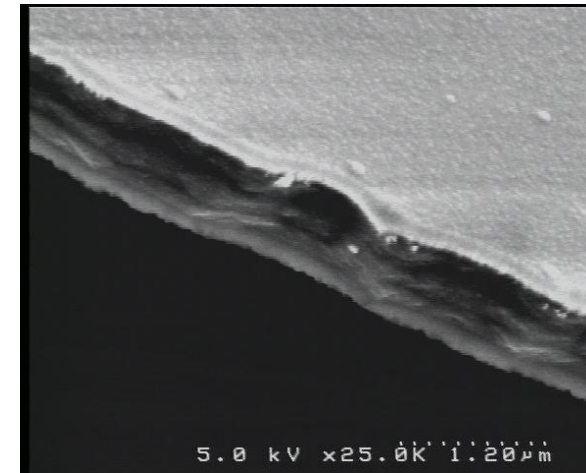
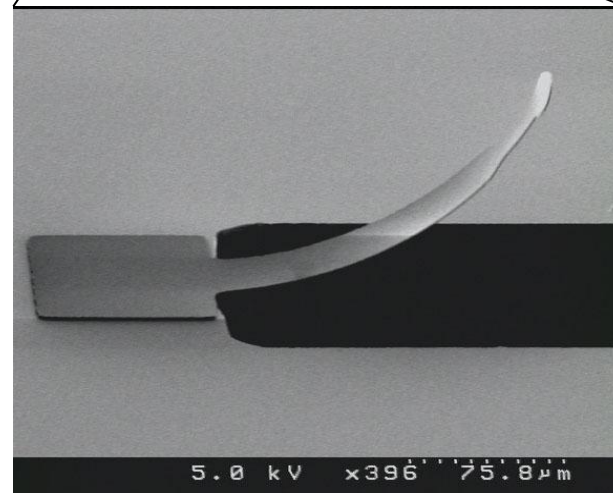
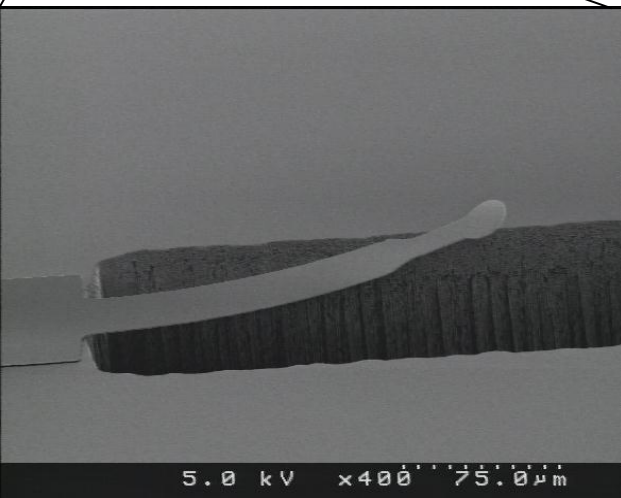


HfO₂
Crystallization

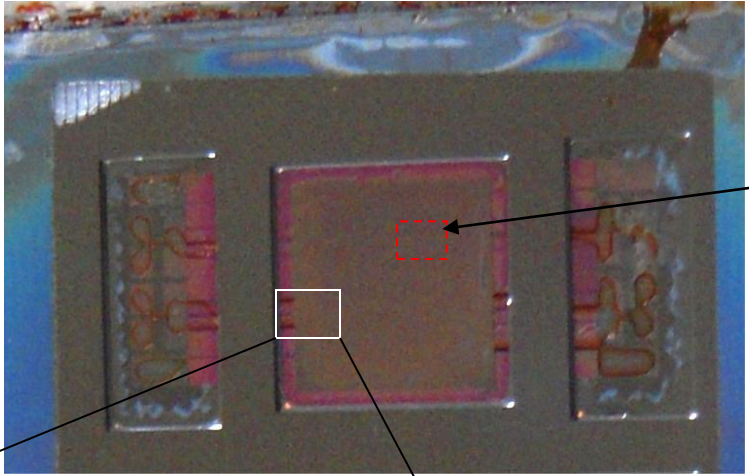
結晶化させた後



Microscope image

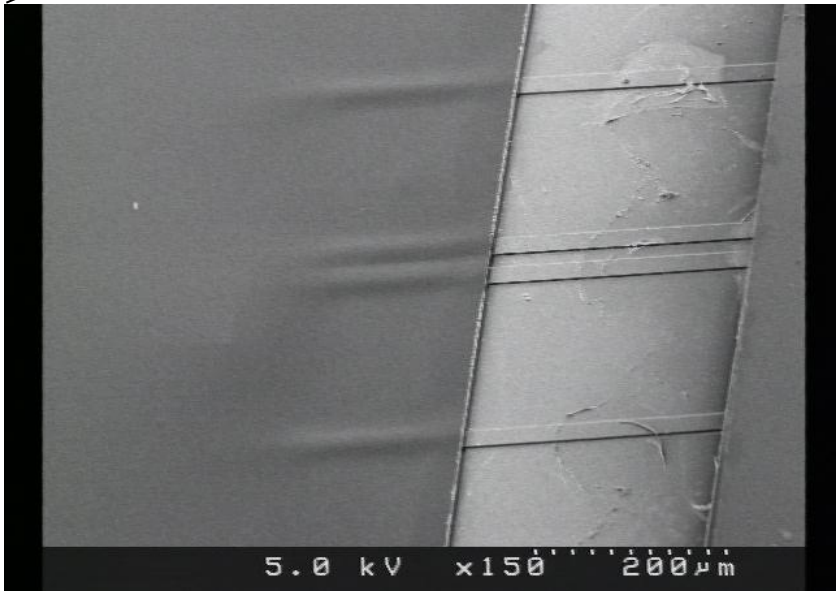


MEMS-DM – Static Deflection Measurement

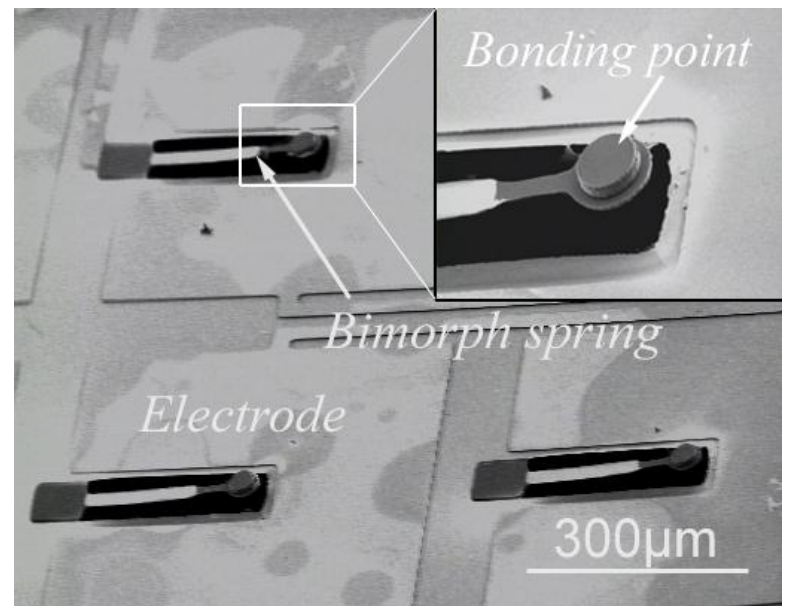


駆動する所
電極面積 $500\mu\text{m} \times 500\mu\text{m}$
測定したミラーエリア
 $900\mu\text{m} \times 670\mu\text{m}$

fabricated Deformable mirror

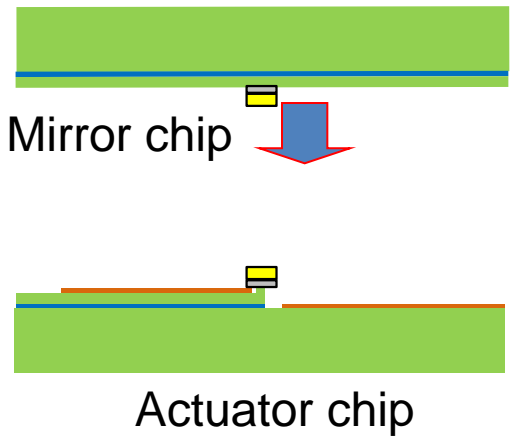


mirror edge stuck to the substrate



bimorph spring array

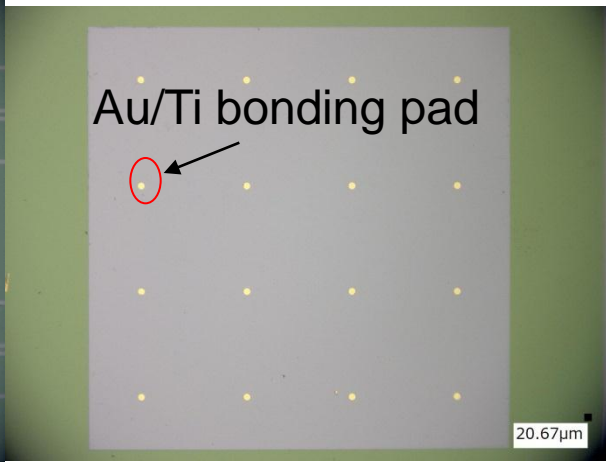
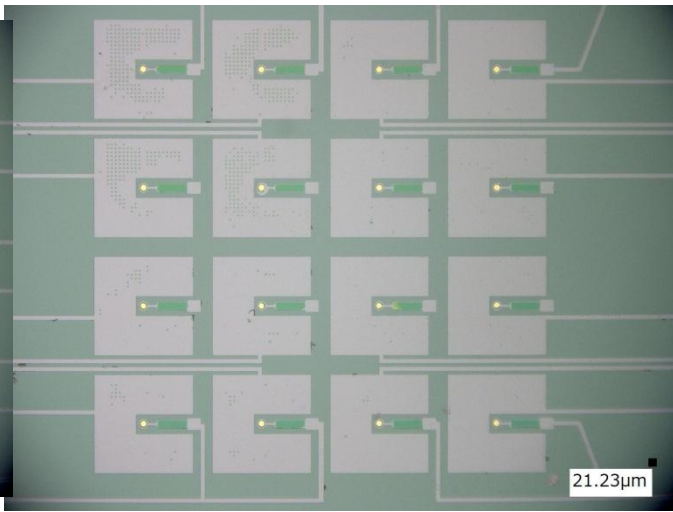
Because the plasma activated bonding requires extremely strict conditions (<2nm surface roughness, high surface cleanliness), another stable bonding process is investigated for the fabrication of MEMS-DM.



Bonding pad: Ti/Au , Ti: 50nm, Au: 200nm;
Ti is used to react with the native oxide layer on the bare Si surface which will result in the poor bond quality of the Au/Si bonding structure.

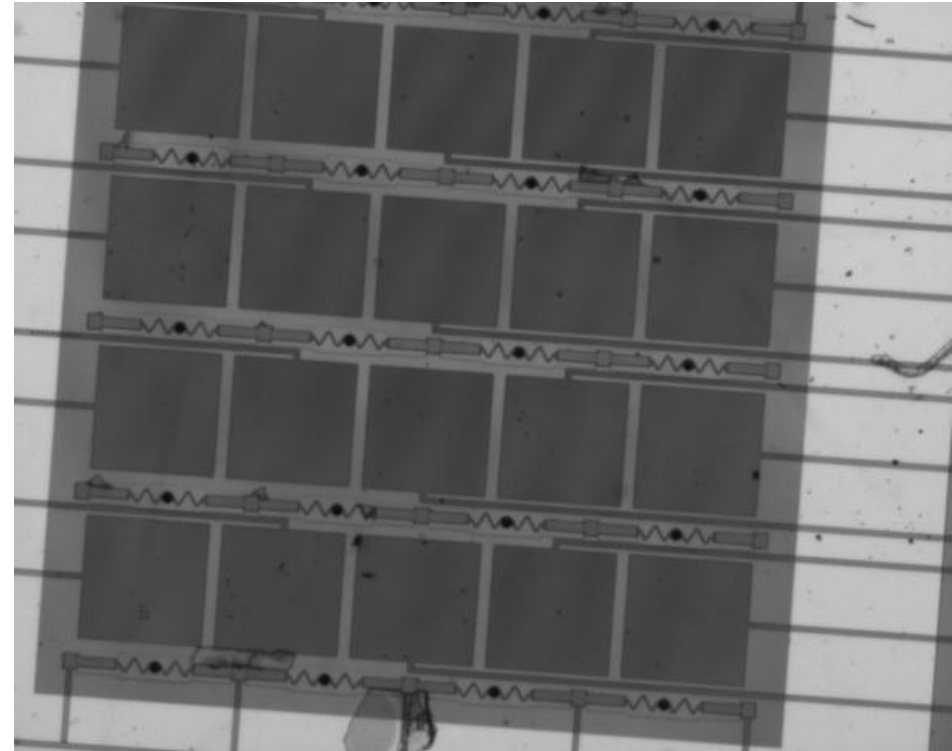
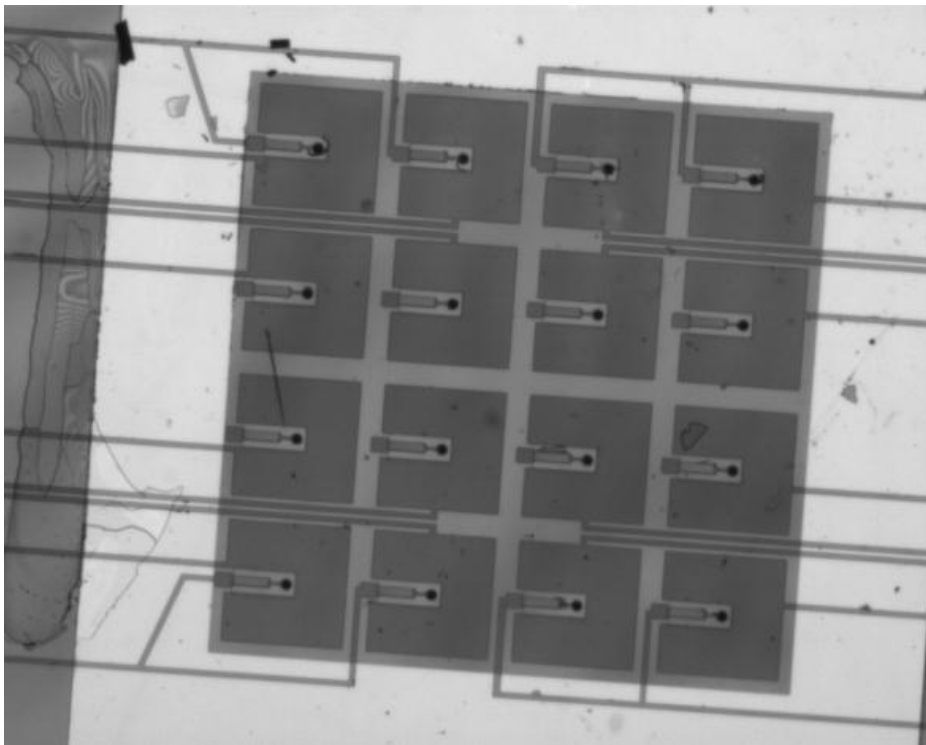


Actuator chip

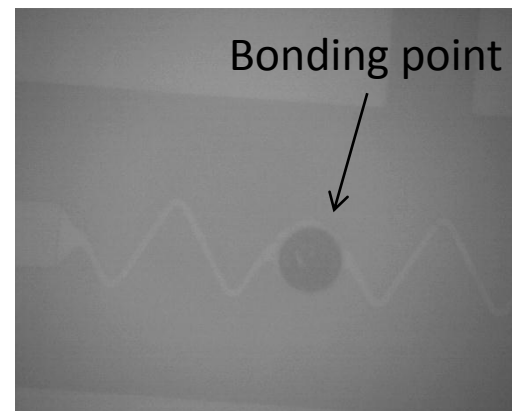
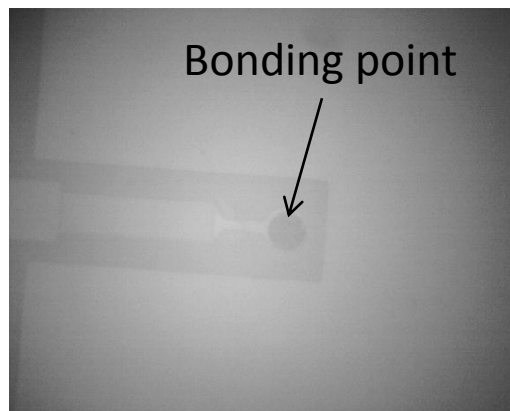


Mirror chip

MEMS-DM – IR micrograph



3.4mm×3.4mm continuous mirror



Bonding point

Bonding point

Bonding condition
Temperature: 400°C
Time: 30min
Pressure: 1.7 MPa
(EVG bonder: 0.4MPa)

1. 光MEMSの紹介

- ・マイクロミラー
- ・可変格子
- ・集積型センサ
- ・Si導波路干渉計

2. 焦点可変デフォーマブルミラーの製作

- ・曲げモーメント駆動による焦点可変ミラー
- ・焦点可変ミラーを備えた光スキャナー
- ・波面補償デフォーマブルミラーの製作